Crystal Growth: Physics, Technology and Modeling

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Lecture 8. Liquid phase epitaxy and lateral overgrowth

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http://www.unipress.waw.pl/~stach/cg-2022-23

Liquid phase epitaxy and lateral overgrowth

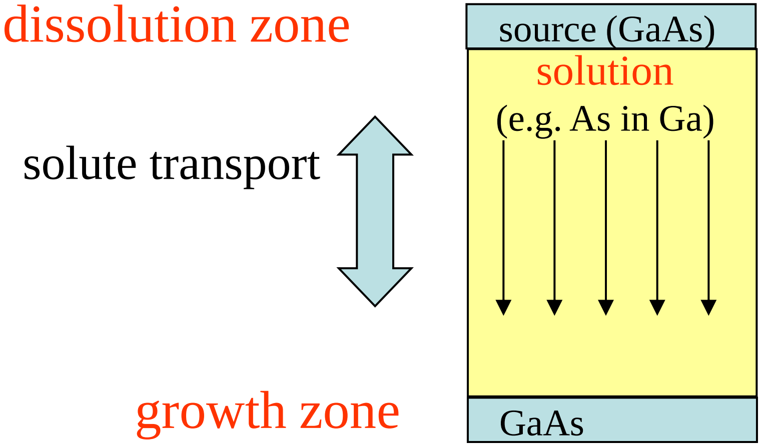
Outline:

- **definition + idea of LPE**
- **history and technical aspects**
- **solute transport during LPE growth; diffusion, convection**
- **Liquid Phase Electroepitaxy**

- **Epitaxial Lateral Overgrowth**
- **principle and growth control**
- **filtration of dislocations in ELO**
- **strain in ELO structures**

Liquid Phase Epitaxy - LPE

technique of epitaxial thin films growth *from metallic solution*



dissolution zone

solute transport

growth zone

source (GaAs)

solution

(e.g. As in Ga)

GaAs

advantages of solution growth & epitaxy

properties of solvent required:

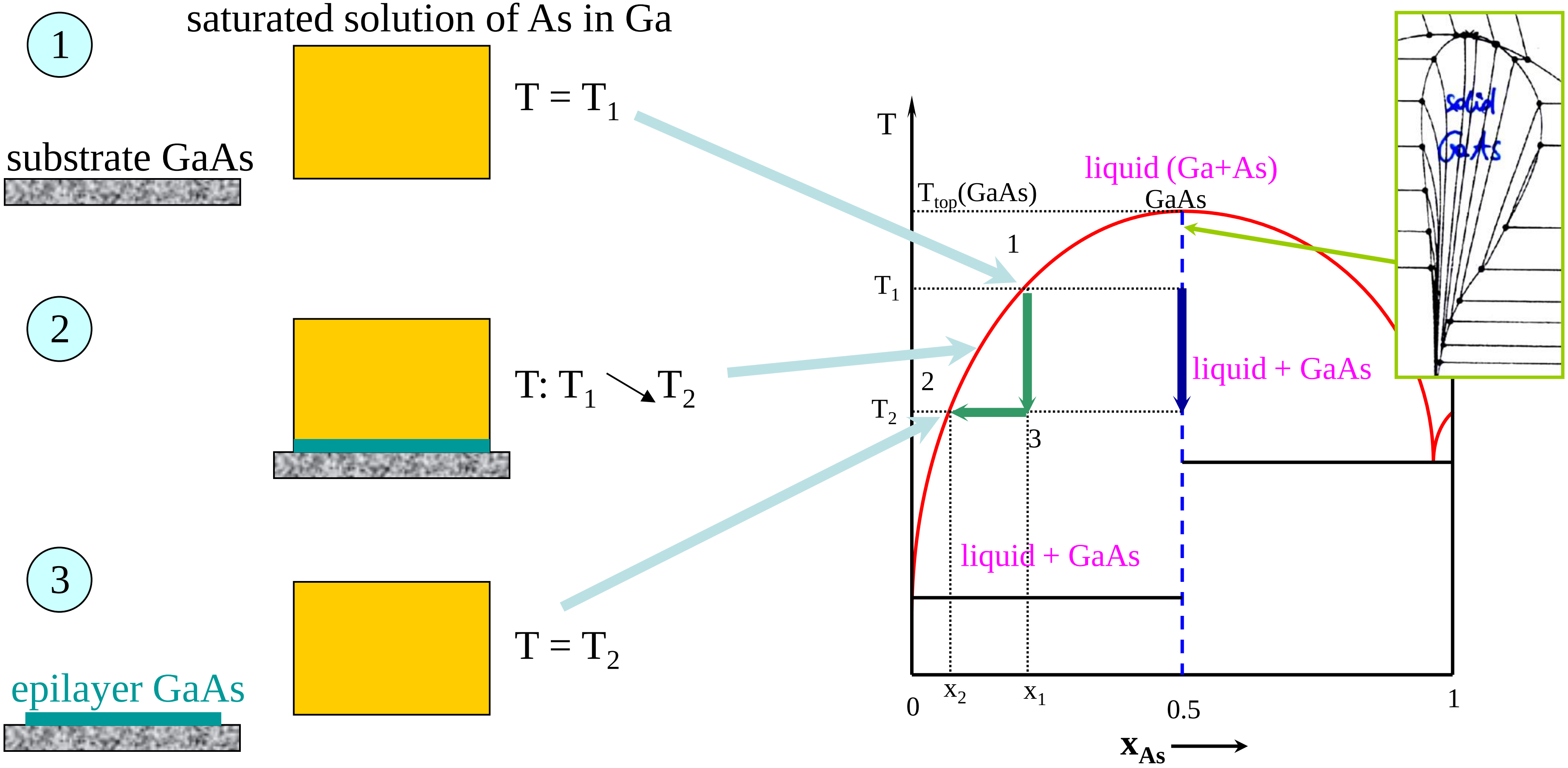
- crystal component (e.g. Ga for GaAs)

  or low solubility in the crystal (Bi, Sn, In, Pb, etc.)
- low melting point
- high solubility of solute @ T_{epi}
- low vapor pressure @ T_{epi}
- high chemical stability
- high purity
- low price ???

Idea of LPE (example: homoepitaxy of GaAs on GaAs substrate)

the Gibbs phase rule: $f_{(\text{degrees of freedom})} = c_{(\text{components})} - p_{(\text{phases})} + 2(p;\,T)$

Ga-As⇔GaAs 2 2 p = const. ⇨ f = 1 (T)



1 saturated solution of As in Ga

substrate GaAs

$T = T_1$

2 $T\text{: } T_1 \searrow T_2$

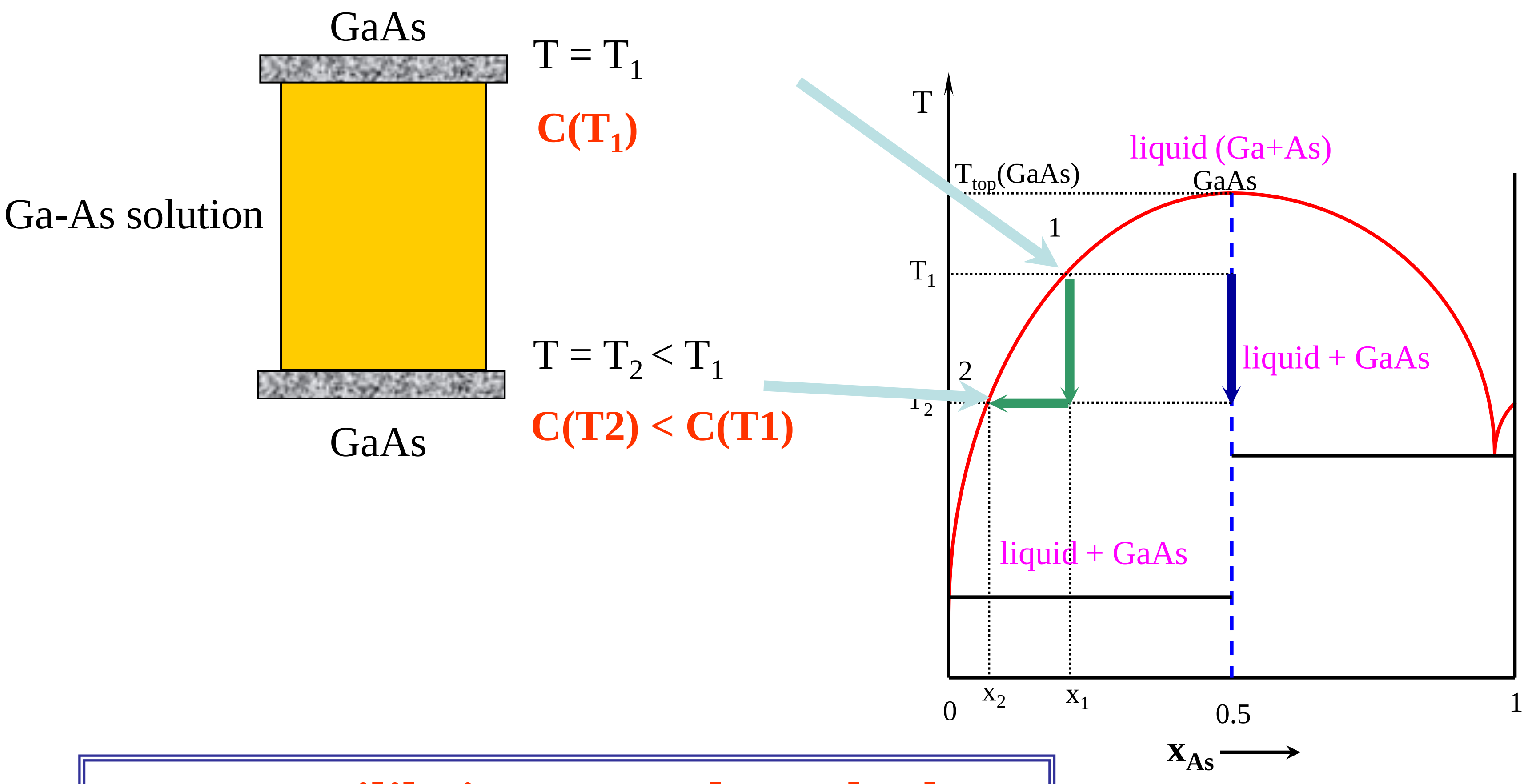
3 $T = T_2$

epilayer GaAs

LPE – equilibrium growth method !!!

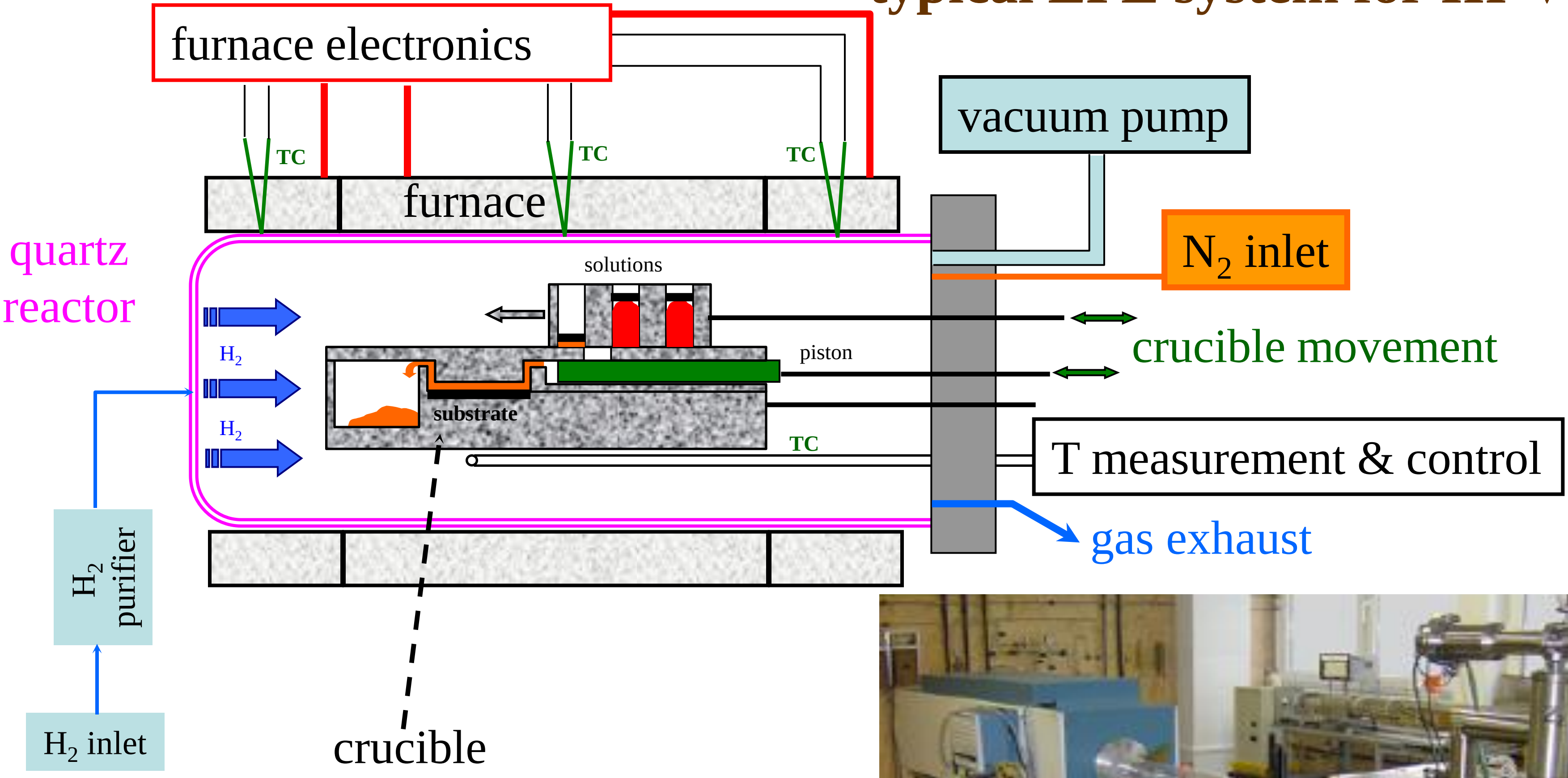
Idea of LPE (example: homoepitaxy of GaAs on GaAs substrate)

growth in T gradient



LPE – equilibrium growth method !!!

typical LPE system for III-V's



furnace electronics

furnace

vacuum pump

N_2 inlet

quartz reactor

crucible movement

T measurement & control

gas exhaust

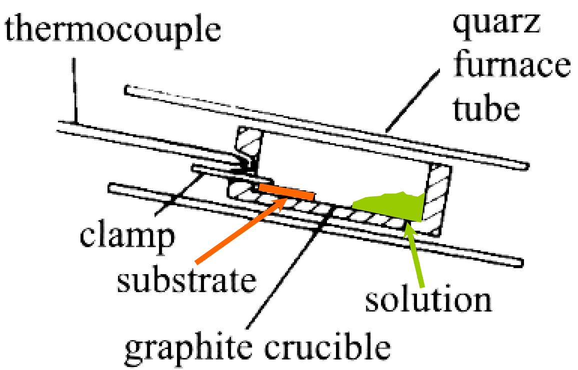
H_2 purifier

H_2 inlet

crucible
(graphite, quartz, …)

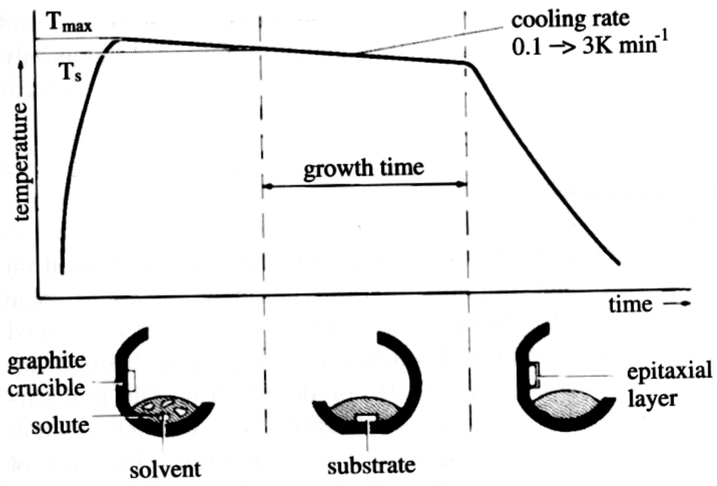
horizontal system
ITE Warszawa

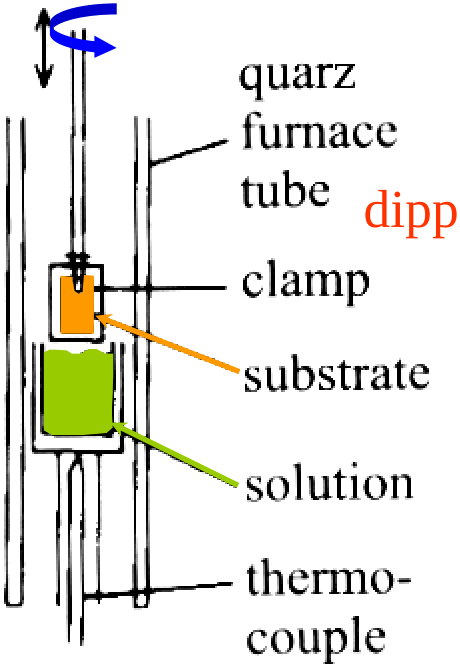
Crucibles in LPE



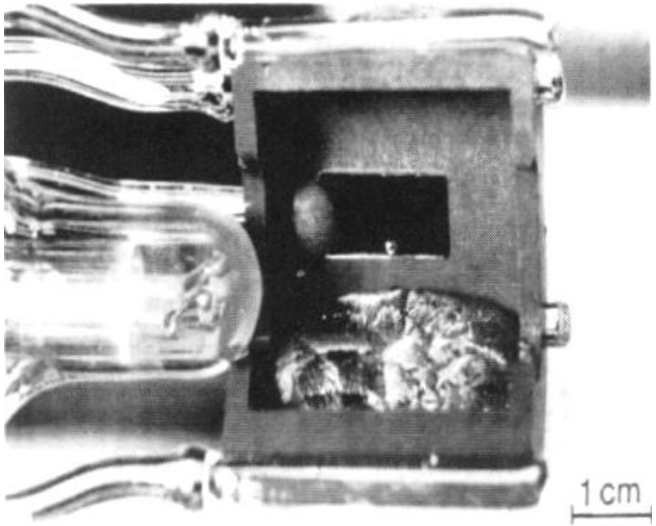
tipping

rotation



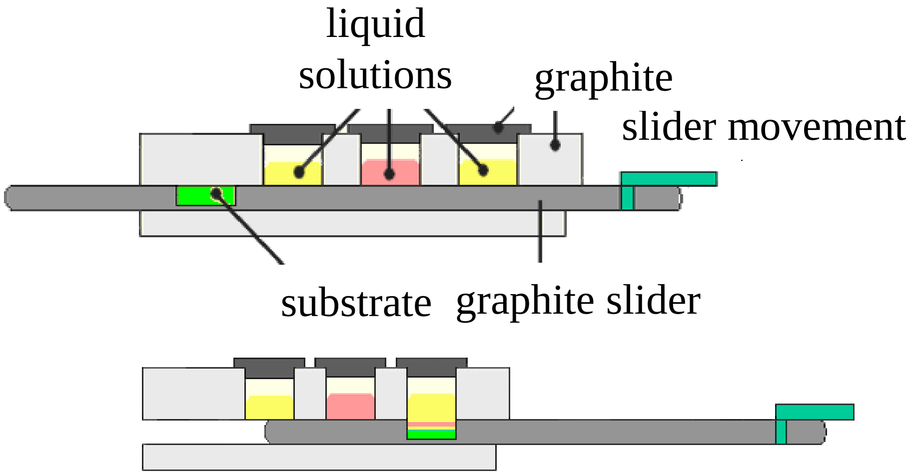


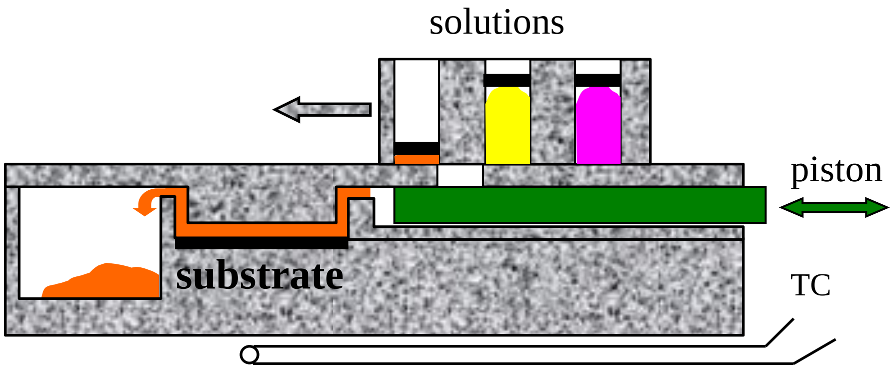
dipping

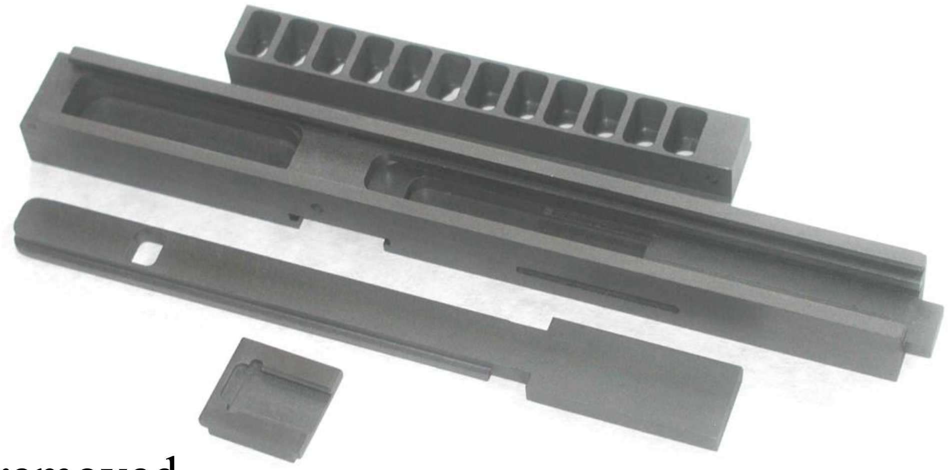


growth of single layers

Crucibles in LPE cont.







IF PAN

advantages:

- growth of multilayer structures
- thin layer of the solution
- „skin” of oxides on the solution surface removed

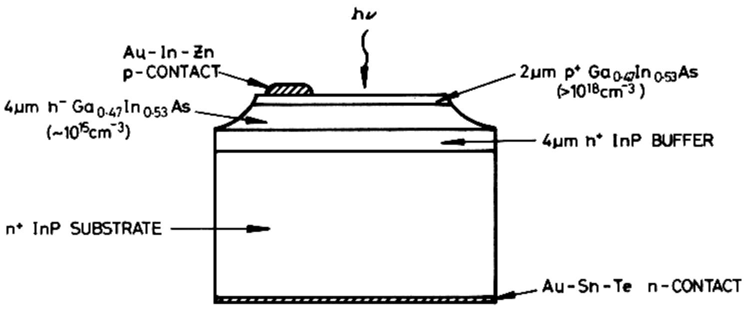
disadvantages:

- blurred (not sharp) interfaces

History

H. Nelson: *Epitaxial growth from the liquid state*
and its application to the fabrication
to the fabrication of tunnel and laser diodes
RCA Rev. 24 (1963) 603.

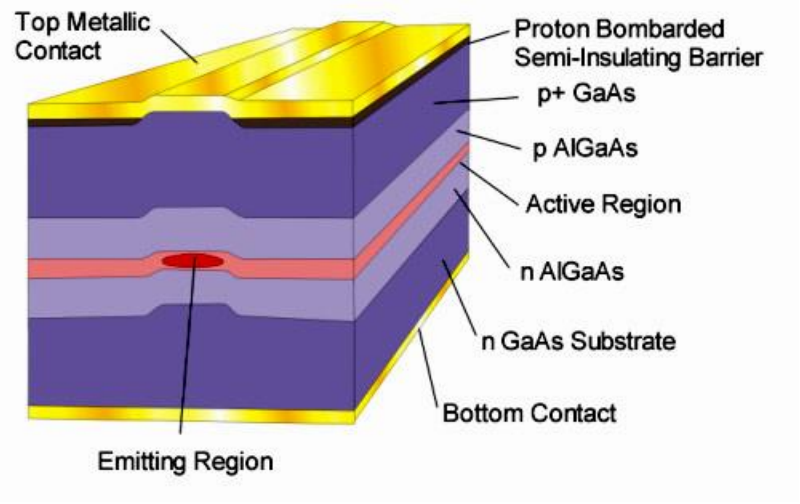
Nobel 2000 - H. Kroemer, J. Kilby, Z. Alfierow
"for developing semiconductor
heterostructures used in high-speed- and opto-electronics"



a. HOMOJUNCTION PHOTODIODE

Why LPE:

- „cheap and easy"
- high purity of layers (impurity segregation)
- selective area growth easy
- broad range of compounds can be grown (As, P, ...)
- „safe" method (as compared to MOVPE)



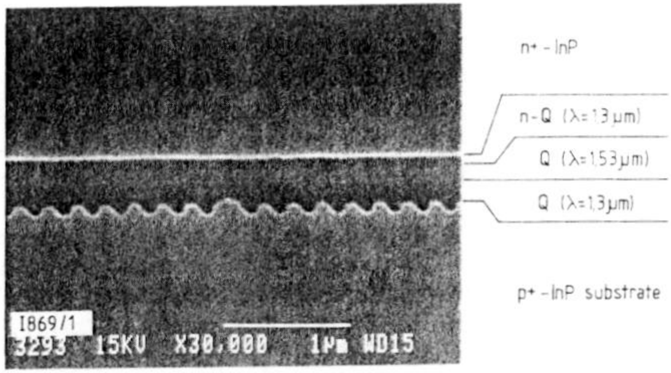
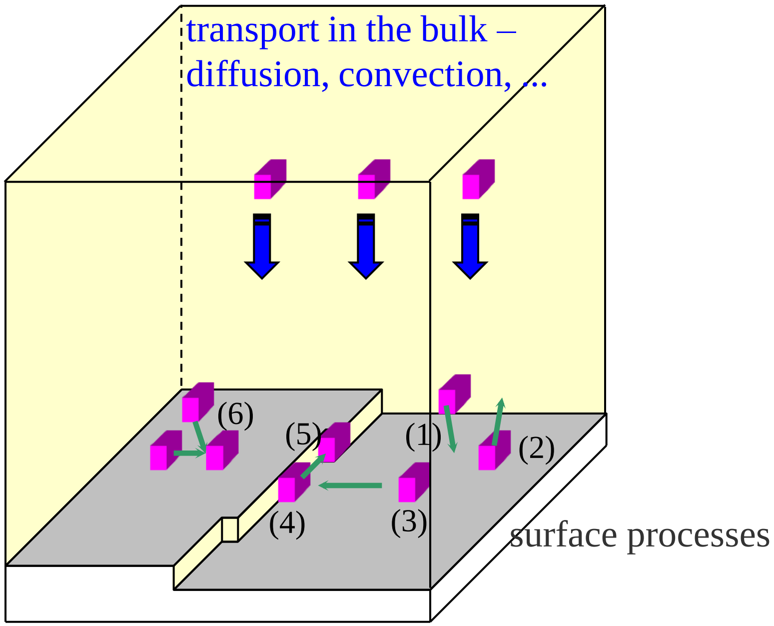


Fig. 14. InGaAsP DFB laser structure grown nearly dissolution-free over a first order grating, after [70]. For details, see text

Growth kinetics



transport of solute in the bulk of solution

↓

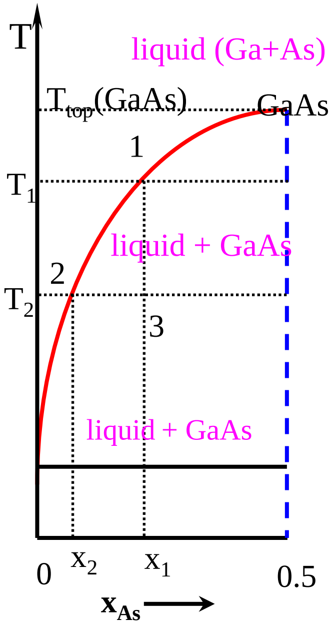
surface processes

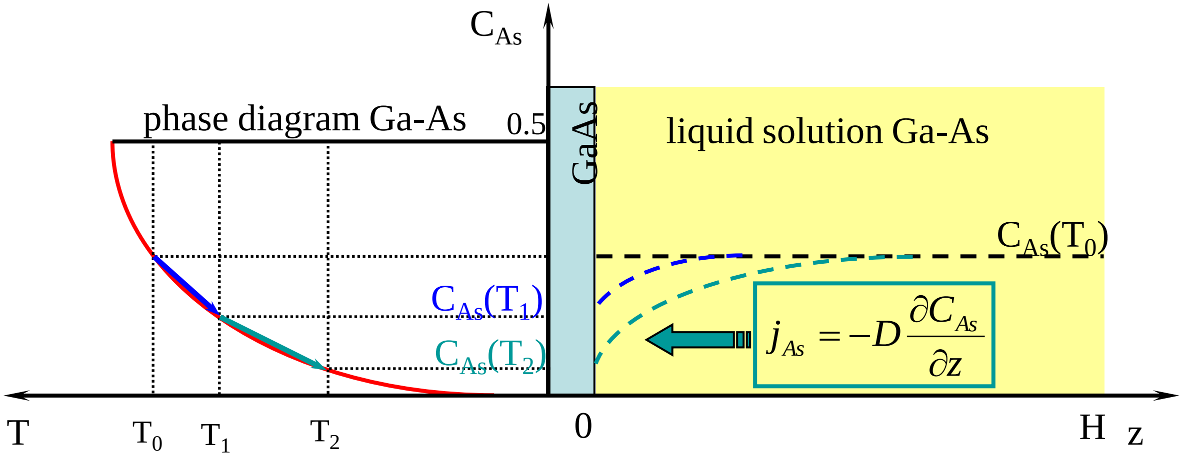
the slower one determines the growth rate

usually

the growth temperature in LPE is so high (surface processes so fast), while the bulk solute transport is slow, that solute transport in the bulk of the solution determines the growth rate

LPE: diffusion controlled growth – example: GaAs growth from Ga-As solution





transport: **mass** **heat**

$$\frac{\partial C}{\partial t} = D\frac{\partial^2 C}{\partial^2 z} + \xcancel{V_{gr}\frac{\partial C}{\partial z}}$$

$$\xcancel{\frac{\partial T}{\partial t} = k\frac{\partial^2 T}{\partial^2 z} + V_{gr}\frac{\partial T}{\partial z}}$$

assumptions:

- fast surface kinetics
- no convective mixing

- low growth rate V_{gr}
- fast heat transport

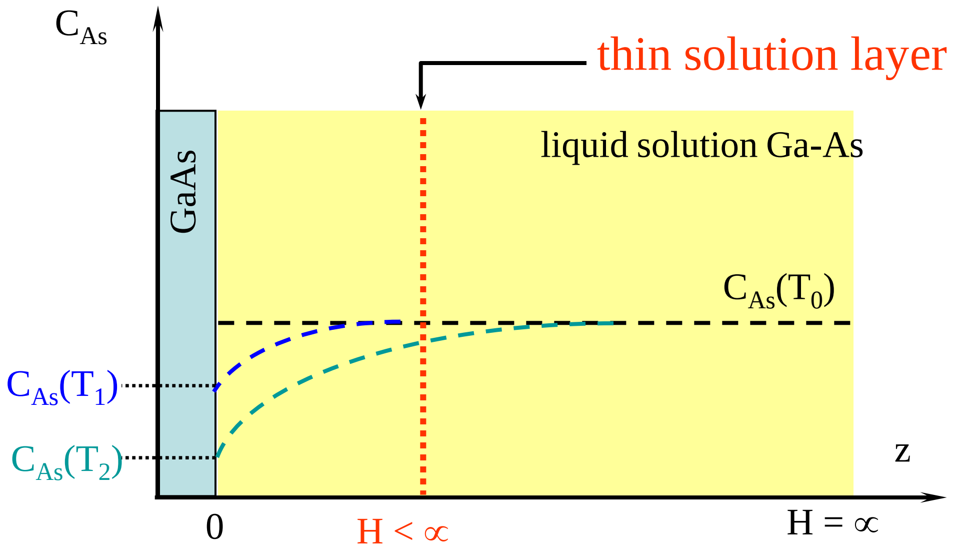
- no diffusion in solid state

mass flux continuity condition

$$V_{gr}\left(C_{s,z=0} - C_{l,z=0}\right) = D_l\frac{\partial C_l}{\partial z}\Big|(z=0) - \xcancel{Ds\frac{\partial C_s}{\partial z}\Big|(z=0)}$$

+ initial and boundary conditions
(which depend on LPE version, e.g. T(t))

LPE: diffusion controlled growth – example: GaAs growth from Ga-As solution



equations

$$\boxed{\frac{\partial C}{\partial t} = D\frac{\partial^2 C}{\partial^2 z}}$$

$$\boxed{V_{gr}\left(C_{s,z=0} - C_{l,z=0}\right) = D_l \frac{\partial C_l}{\partial z}\Big|(z=0)}$$

infinite solution

$$H = \infty \Leftrightarrow H >> \sqrt{D_l t}$$

$$\text{Ga-As: } T = 800^o C \quad D_l \approx 4 \cdot 10^{-5}\ \text{cm}^2/\text{s}$$

$$t = 30\ \text{min} \quad \sqrt{Dt} = 2.6\ \text{mm}$$

initial and boundary conditions

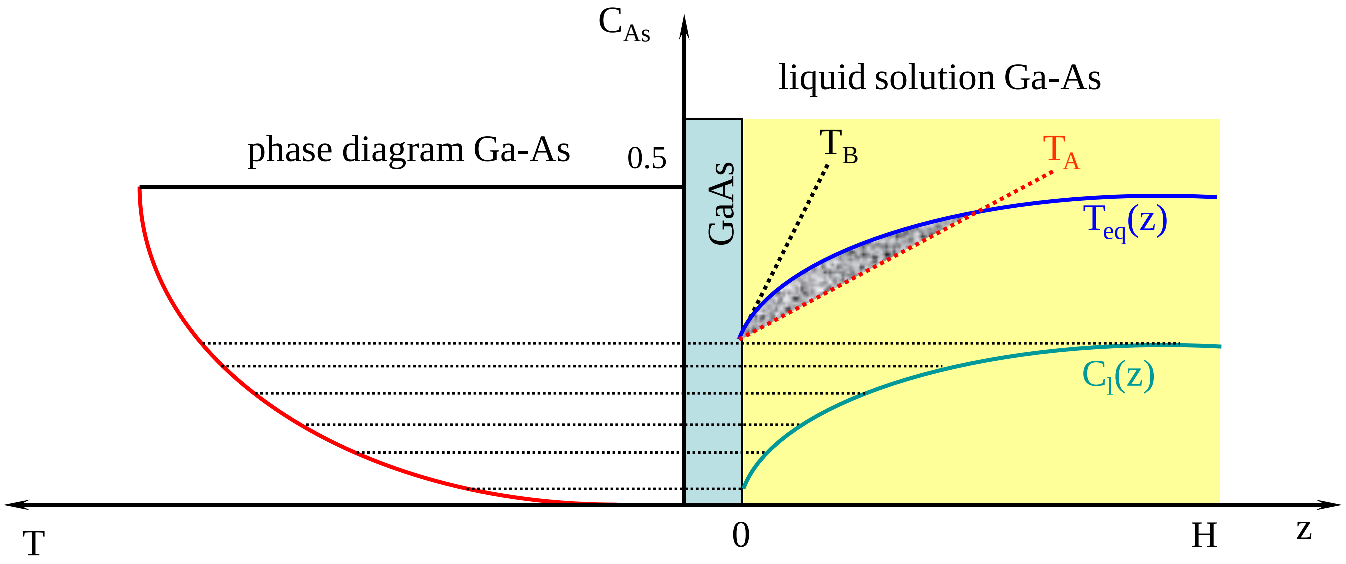
$$\boxed{C_l(z=0,t) = C_{eq}(T(t))}$$

$$\boxed{\frac{\partial C_l}{\partial z}(z \to \infty, t) = 0}$$

equilibrium at the
solid/liquid interface

LPE version

LPE: constitutional supersaturation



theory:

increase grad T at the interface

(T_B instead of T_A)

Udayashankar et al., Bull. Mater. Sci 26 *(2003) 685*

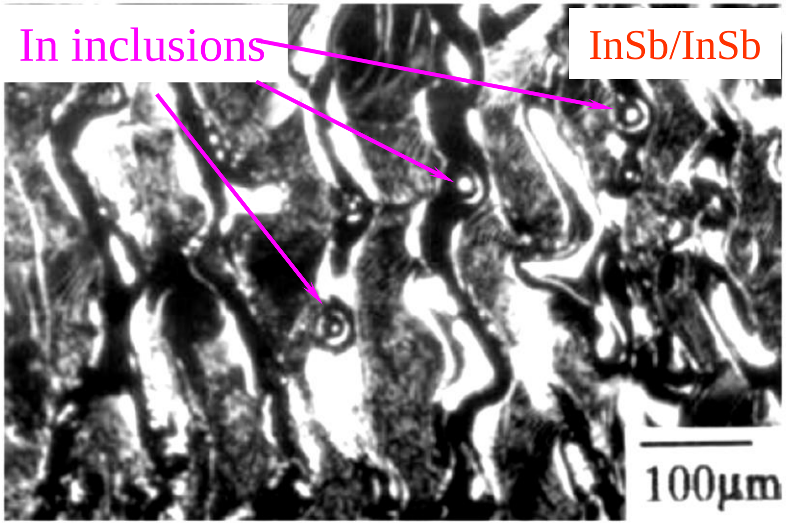
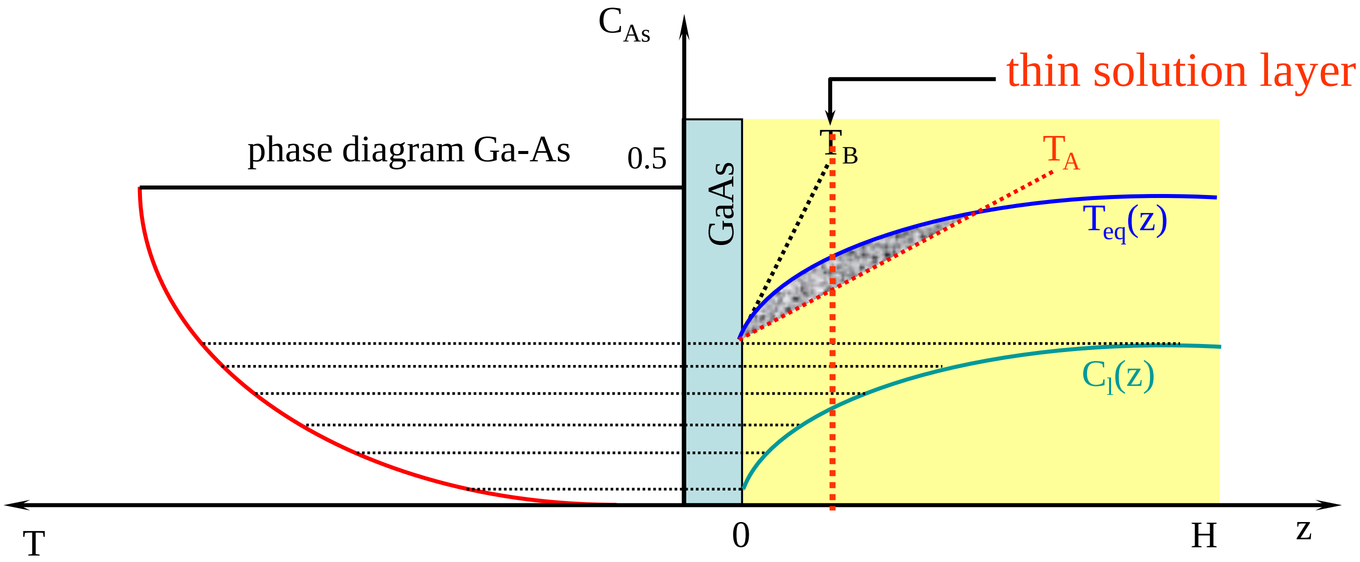


Figure 3. Film showing various surface features like ridges, valleys, inclusions, etc.

LPE: constitutional supersaturation



theory:

increase grad T at the interface (T_B instead of T_A)

practice:

decrease concentration gradient

- thinner solution layer
- lower the growth rate

Udayashankar et al., Bull. Mater. Sci *26* *(2003) 685*

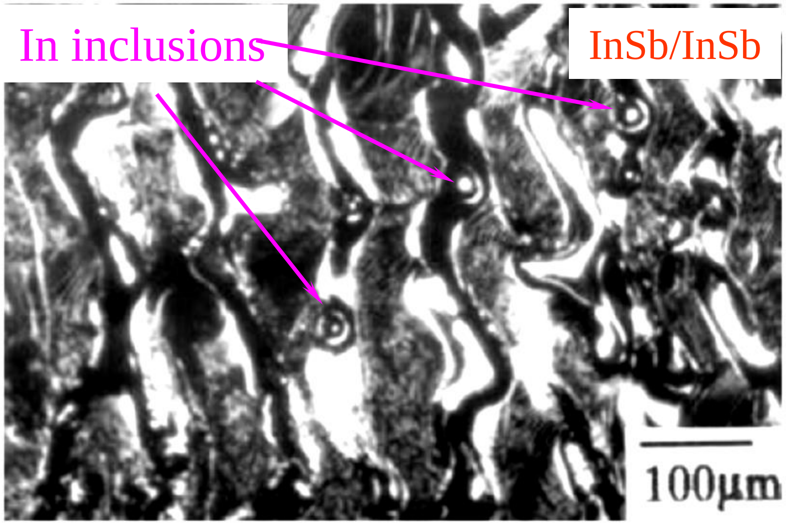


Figure 3. Film showing various surface features like ridges, valleys, inclusions, etc.

LPE: natural convection

natural convection

$\rho = \rho(T, C)$ + gravity

convection thermal solutal

$\frac{\partial \rho}{\partial T} < 0$ $\frac{\partial \rho}{\partial C}$???

<u>assumptions:</u>

- no external mixing
- vertical substrate
- T(x, y, z) = const.

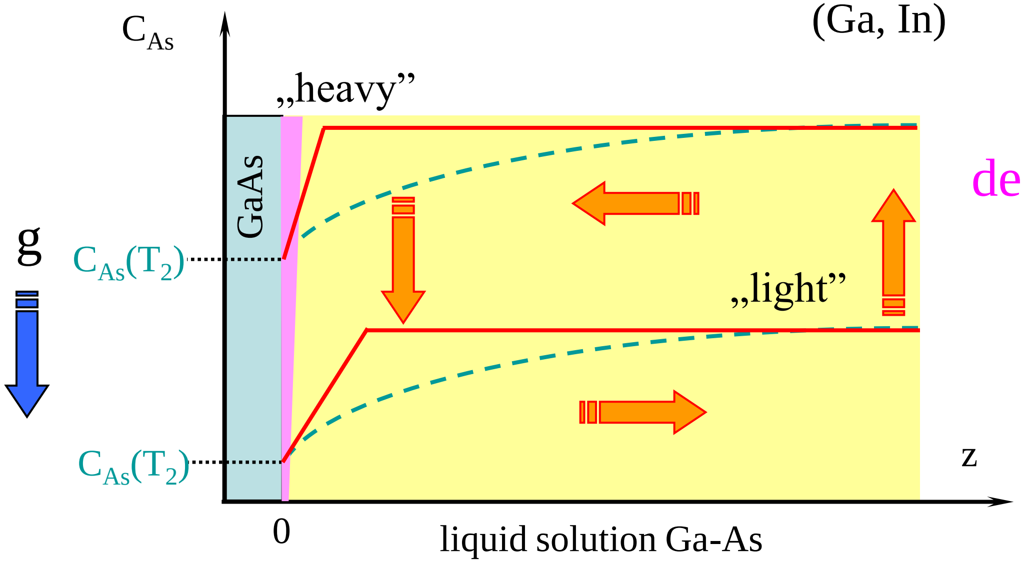
<u>solutal convection only</u>

typical III-V solutions

$\rho_{solvent} > \rho_{solute}$

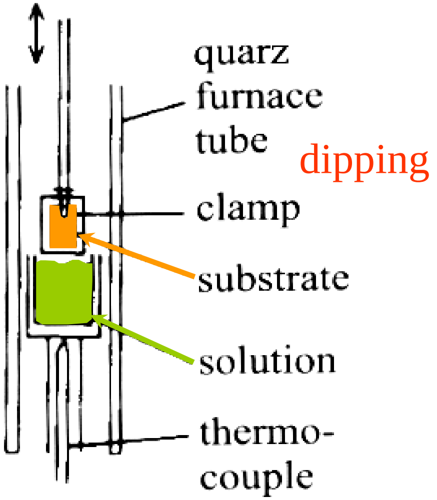
(Ga, In) (As, P)

$$\boxed{\frac{\partial \rho}{\partial C} < 0}$$



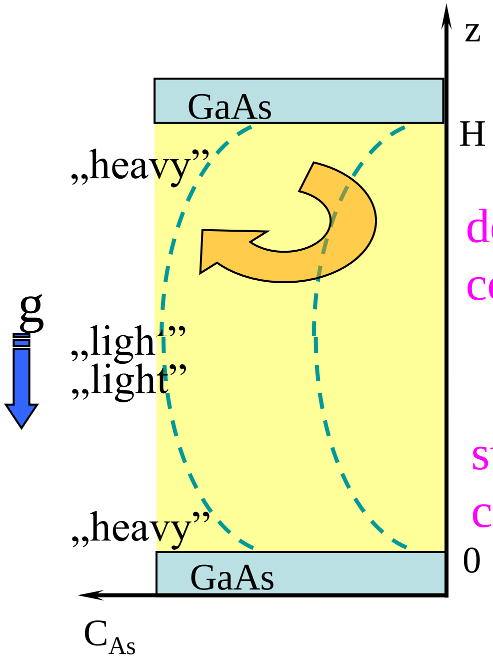
destabilizing solute distribution (As)

epilayer thickness gradient



LPE: natural convection cont.

S. Krukowski's lecture



destabilizing solute (As) concentration distribution

stabilizing solute (As) concentration distribution

if the Rayleigh's number is low Ra (<1000)

diffusion dominates

usually both gradT and gradC exist

$$Ra_C = g \cdot \Delta C \cdot \beta \cdot H^3 / D\nu < 1000$$

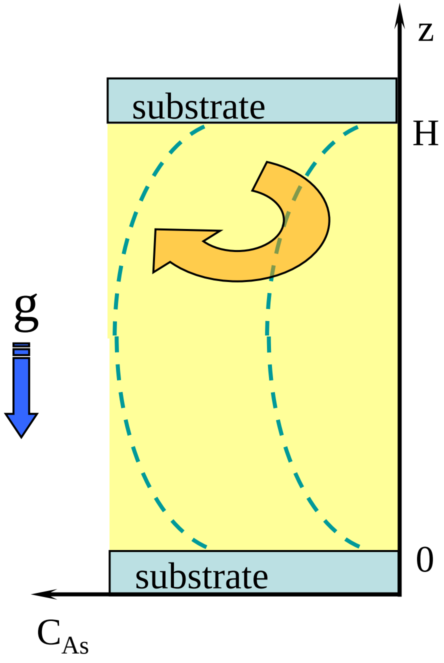
$$Ra_T = g \cdot \Delta T \cdot \alpha \cdot H^3 / \kappa\nu < 1000$$

- κ >> D – small ΔC leads to convective flow
- solutal convection >> thermal convection
- Ra ~ H^3 - solution layer thickness !!!

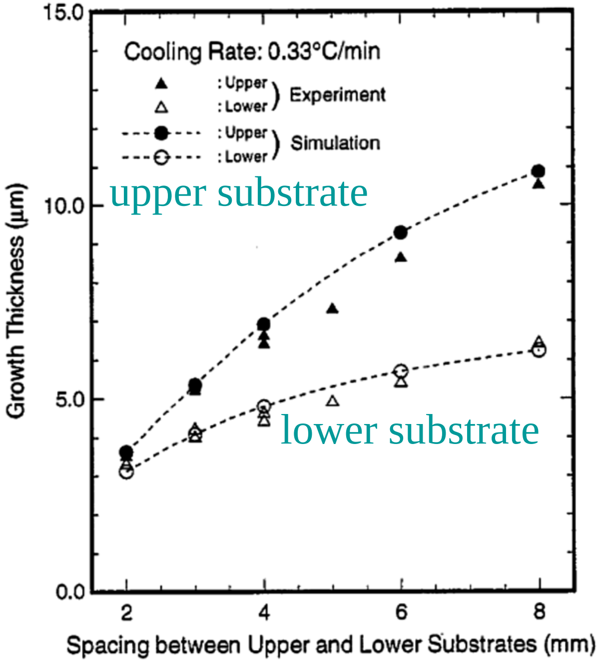
Tiller JCG 2 (1968) 69: no thermal convection if H < 5 mm
no solutal convection if H < 2 mm

LPE from thin solution layer !!!

LPE: natural convection cont.



Kimura et al. JCG 167 (1996) 516

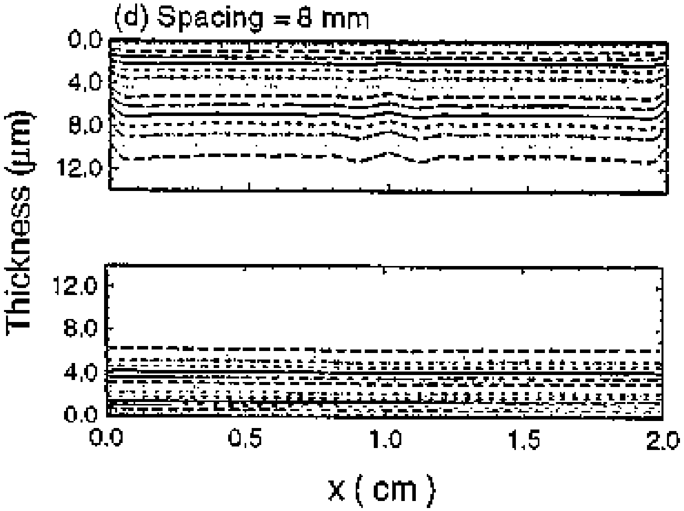


upper substrate

lower substrate

LPE of Si from Sn solution

simulation + exp.

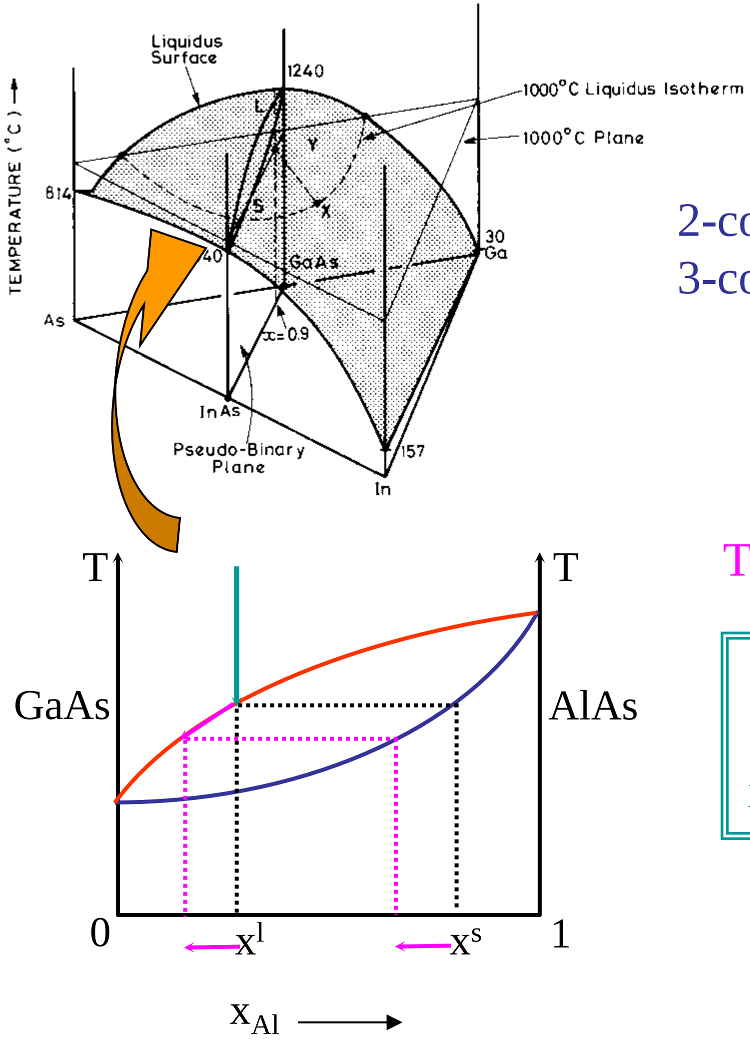


for thin solutions growth
on both substrates similar

LPE of multicomponent systems (example: GaAlAs on GaAs)

the Gibbs phase rule: $f_{(\text{degrees of freedom})} = c_{(\text{components})} - p_{(\text{phases})} + 2(p;\ T)$

e.g. Ga-Al-As ⇔ $Ga_{1-x}Al_xAs$ 3 2 p = const. ⇨ f = 2 (T, x)



2-component system: composition of epilayer fixed

3-component system: composition of epilayer (x) - variable

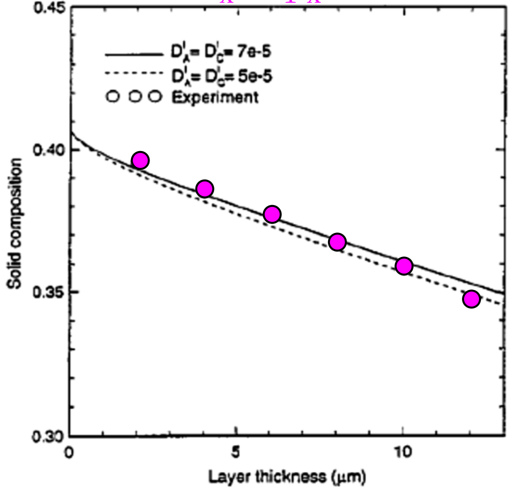
T↓ - grad x^s

T = const.

⇩

x^s = const.

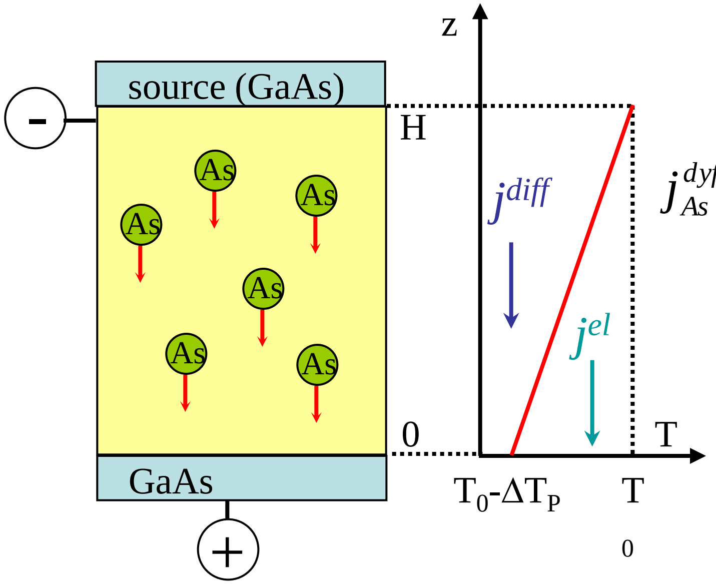
LPE: $Al_xGa_{1-x}As/GaAs$



LPE growth of compositionally uniform AlGaAs layers challenging

Liquid phase electroepitaxy (LPEE)

T_0 = const. + DC current flow through the solid/liquid interface



Peltier effect

$$j_{As}^{dyf} = D\cdot\frac{C(T_0)-C(T_0-\Delta T_P)}{H}$$

$$= D\cdot {dC}/{dT}\cdot {\Delta T_P}/{H}$$

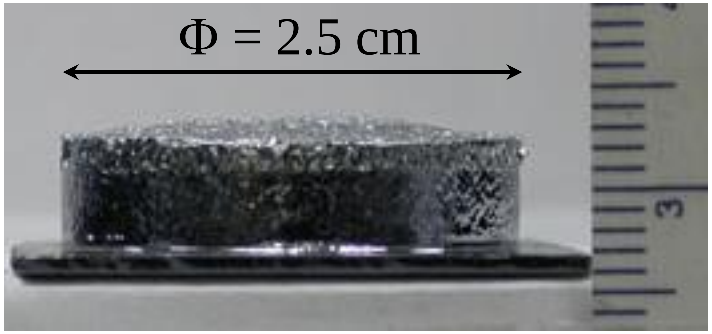
electrotransport

„electron wind" effect

$$j_{As}^{el} = \mu\cdot E\cdot C(T_0)$$

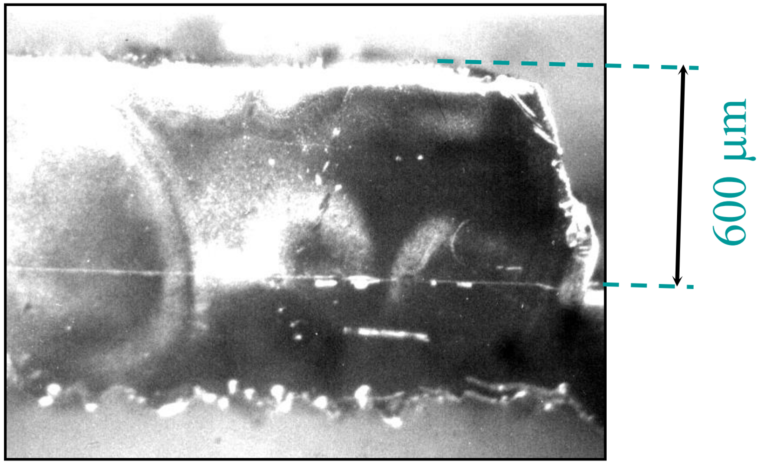
$$= \mu\cdot\sigma\cdot j_e\cdot C(T_0)$$

$$\boxed{V_{gr} \propto \textit{electric current density}}$$



LPEE InGaAs/GaAs

S. Dost, Univ.Victoria, BC, Canada



LPEE AlGaSb/GaSb

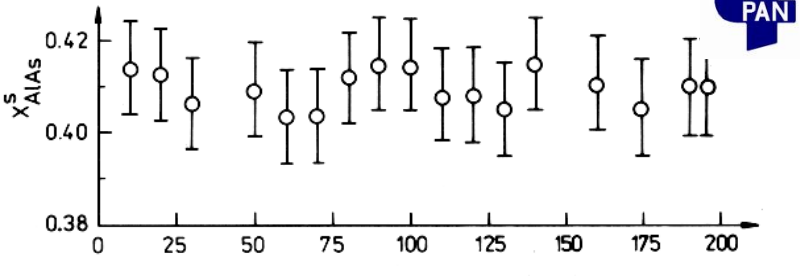
Z.R. Zytkiewicz, IF PAN

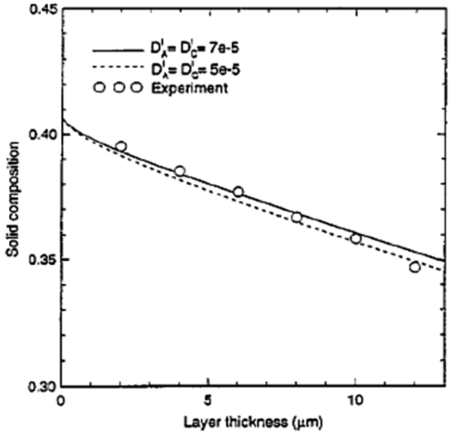
LPEE - advantages

- compositional uniformity
- *in situ* monitoring
- time markers
- simultaneous growth of many crystals
- „easier” V_{gr} control ~ current density
- surface stability

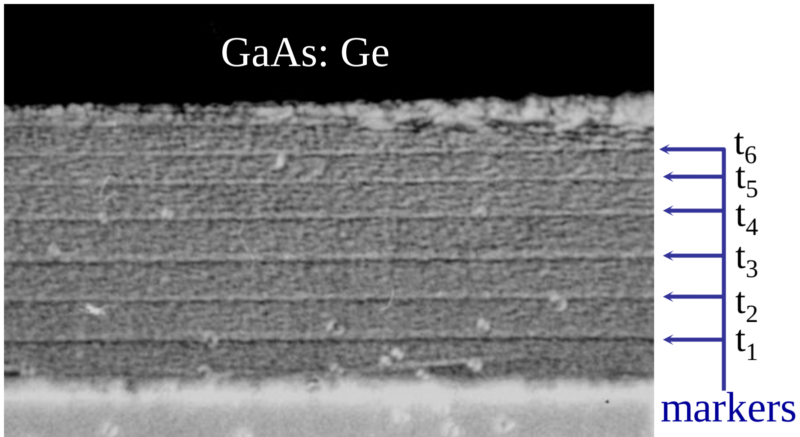
T = const.

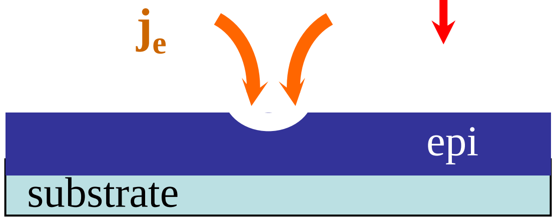
LPEE $Al_xGa_{1-x}As/GaAs$

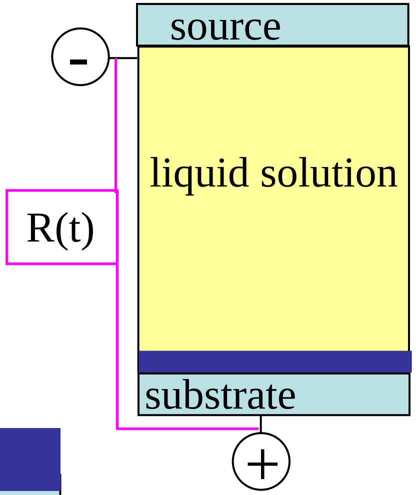


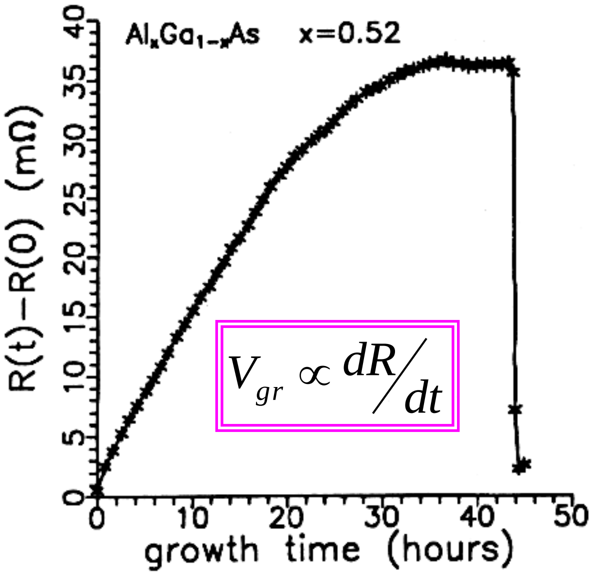


LPE $Al_xGa_{1-x}As/GaAs$



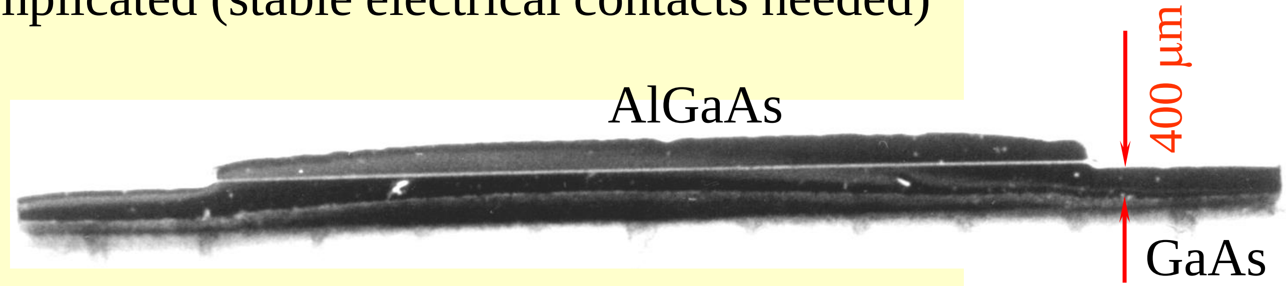






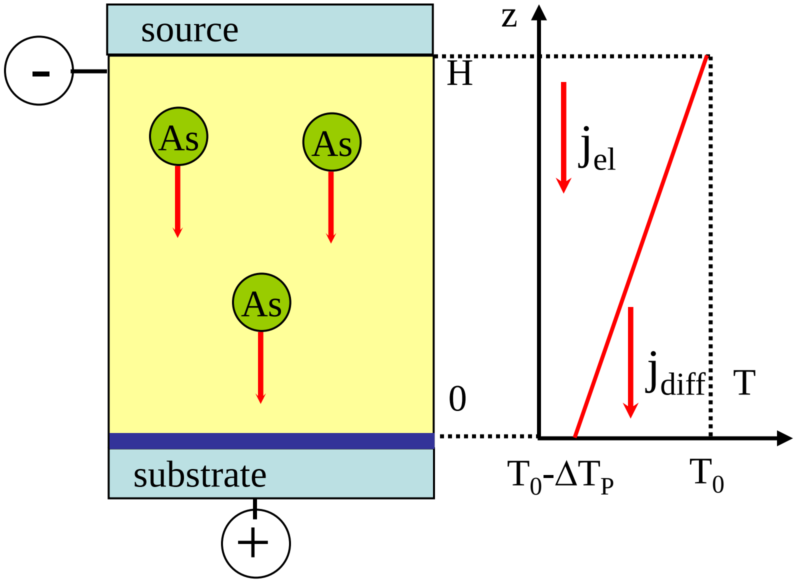
LPEE - disadvantages

- LPEE system more complicated (stable electrical contacts needed)

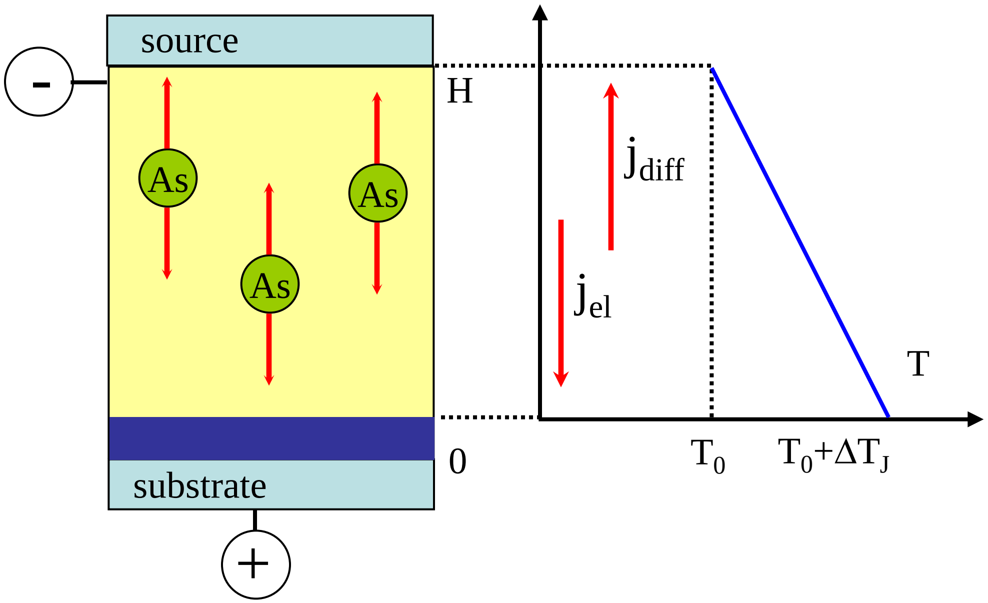


- Joule effect limiting the crystal thickness

no Joule effect

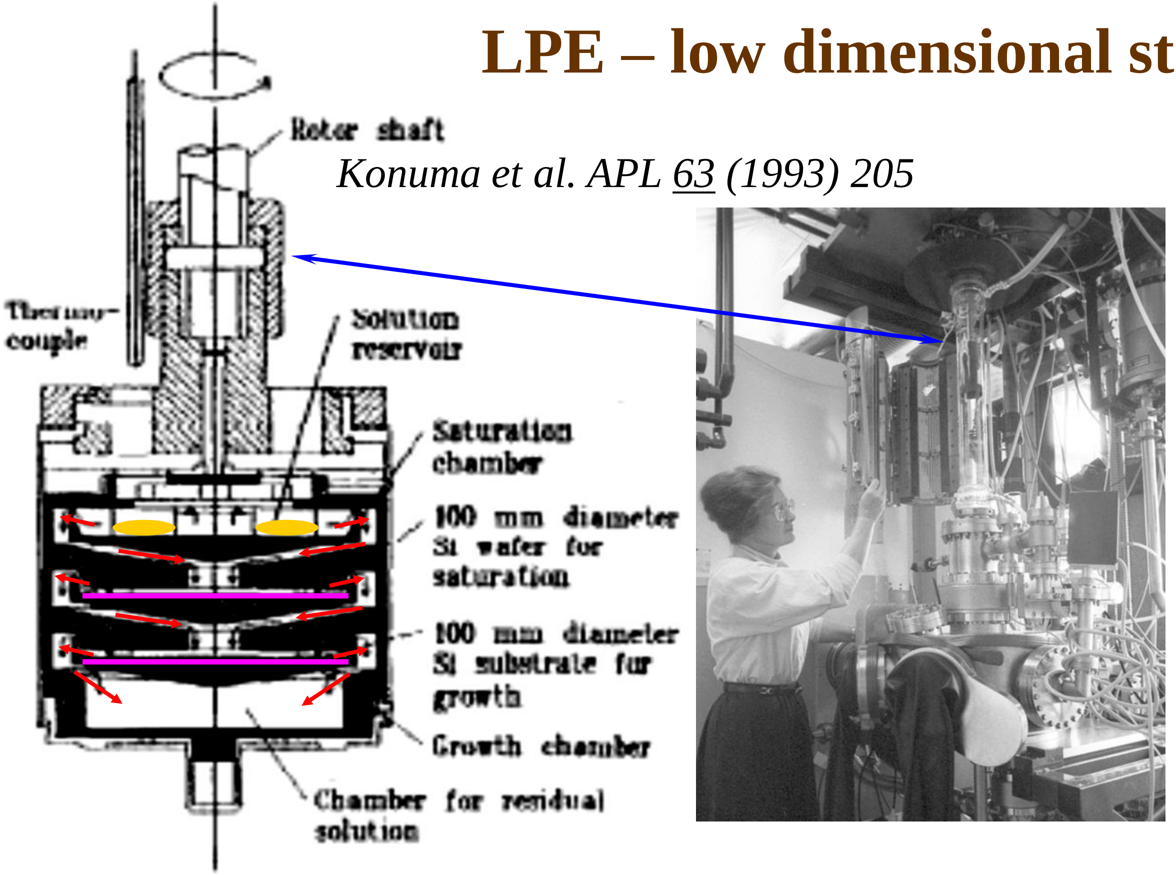


with Joule effect



growth can be continued if j_{el} ↓

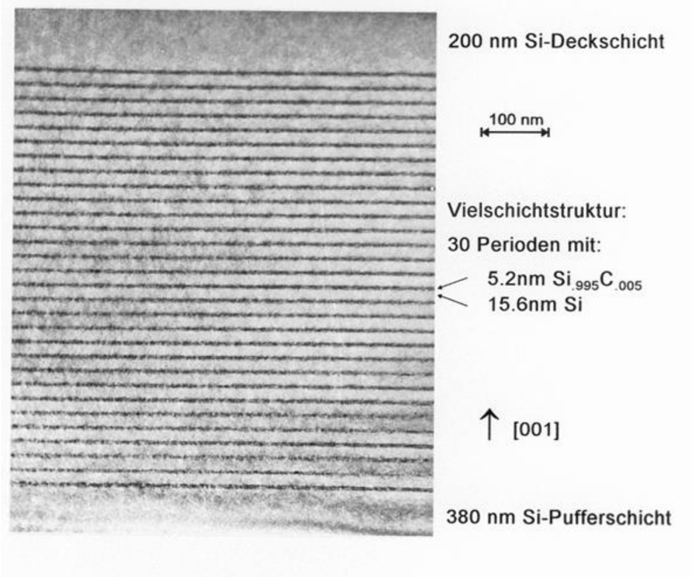
LPE – low dimensional structures



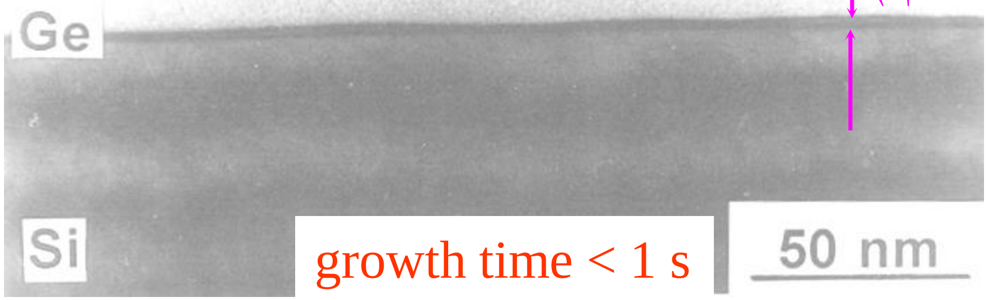
Konuma et al. APL 63 (1993) 205

4” substrate !!!

Si 15.6 nm/$Si_{0.995}C_{0.005}$ 5.2 nm

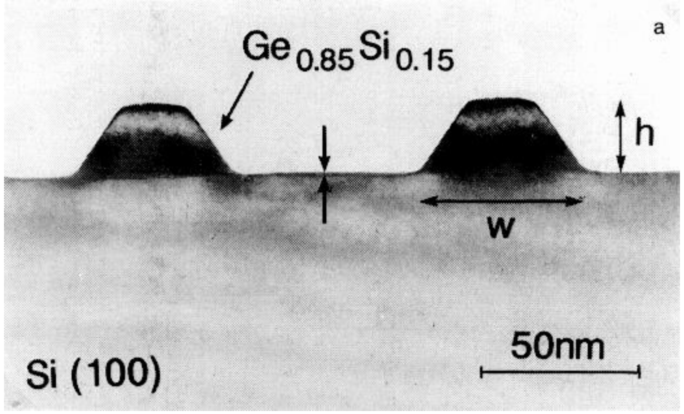


pseudomorphic growth of Ge on Si



growth time < 1 s

SiGe/Si QDs



LPE - summary

LPE

solution growth:

- low concentration of point defects
- high purity of the layers (segregation of impurities)
- selective area epitaxy easy
- wide range of compounds

epitaxy:

- ordered growth of multilayer crystalline structures

- technically simple (standard version)
- „cheap and easy"
- „safe" technique
- growth rate ~µm/min
- growth of low-dimensional structures very difficult

disadvantages:

limitations due to equilibrium nature of LPE growth

- doping limited by phase diagram (e.g. GaAs:Mn)
- structures requiring a high supersaturation (GaAs/Si) difficult to fabricate
- systems with limited solubility in solid (phase separation) difficult to grow

- no *in situ* growth monitoring possible (some possibilities in LPEE)

LPE considered as „old fashion" technology – wrong !!!
Every technology is important and valuable if properly used

for further reading on LPE

Handbook of Crystal Growth, Ed. D.T.J. Hurle
vol. 3, Elsevier 1994

- E. Bauser *Atomic mechanisms in semiconductor Liquid Phase Epitaxy*
- M.B. Small, E.A. Giess and R. Ghez *Liquid Phase Epitaxy*

E. Kuphal *Liquid Phase Epitaxy* Appl. Phys. <u>A52</u> (1991) 380.

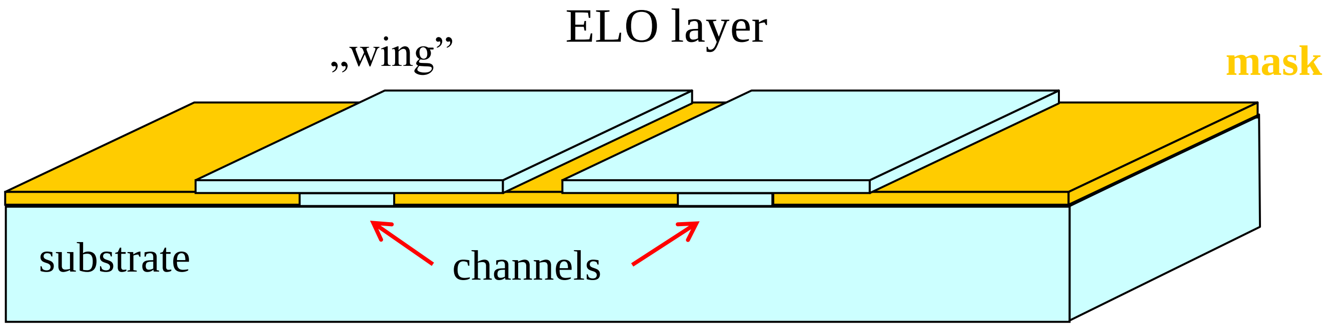
M.B. Small, I. Crossley *The physical processes occurring during liquid phase epitaxial growth* J. Cryst. Growth <u>27</u> (1974) 35.

M.G. Astles *Liquid Phase Epitaxial Growth of III-V Compound Semiconductor Materials and their Device Applications*, IOP Publishing 1990.

B. Pamplin (ed.) *Crystal growth*, Pergamon, 1974

K. Sangwal (ed.) *Elementary Crystal Growth*, SAAN Publishers, 1994.

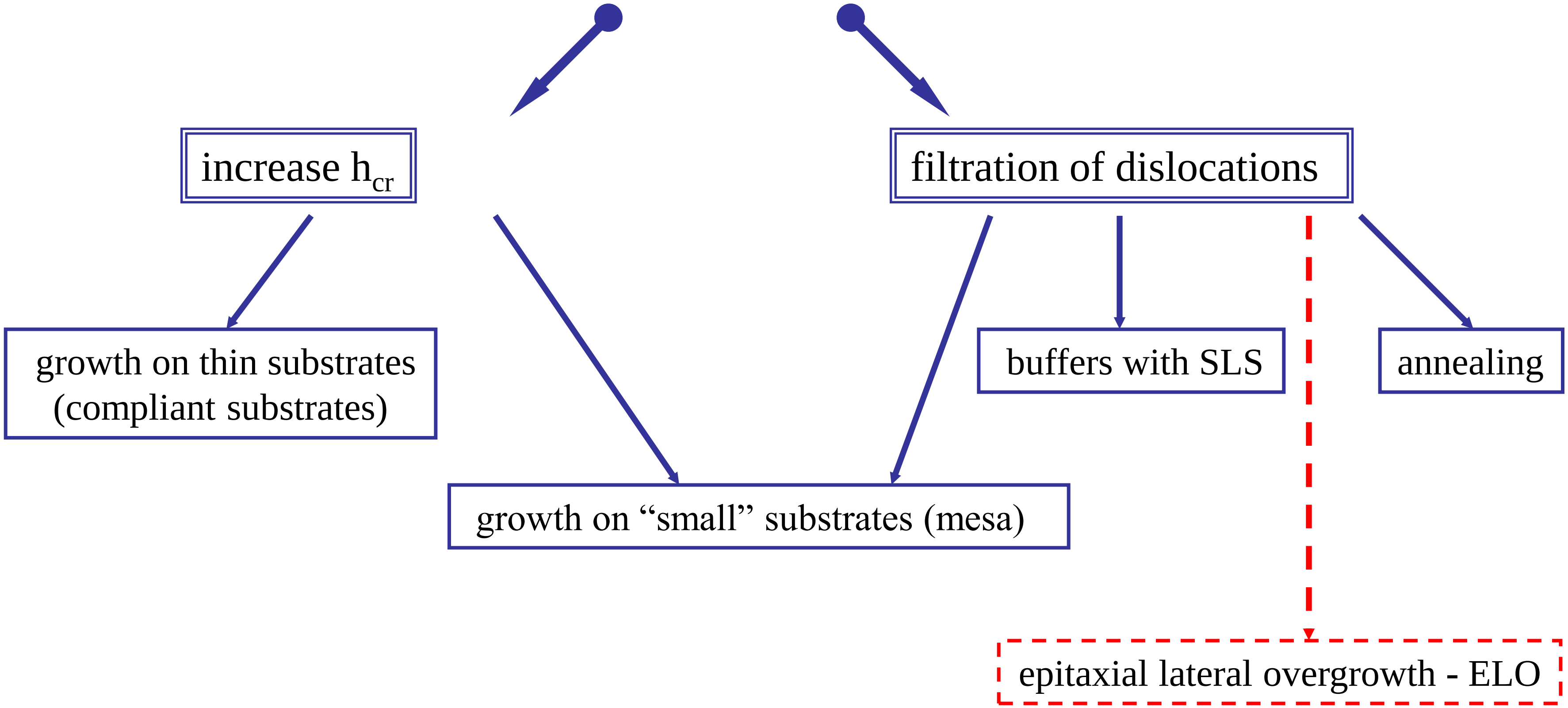
Epitaxial Lateral Overgrowth (ELO)



requirements:

- **high growth selectivity (no nucleation on the mask)**
- **fast lateral (horizontal) growth V_{lat}**
- **slow normal (vertical) growth V_{ver}**

Methods to reduce defect density in lattice mismatched epitaxial structures - summary



increase h_{cr}

filtration of dislocations

growth on thin substrates (compliant substrates)

growth on “small” substrates (mesa)

buffers with SLS

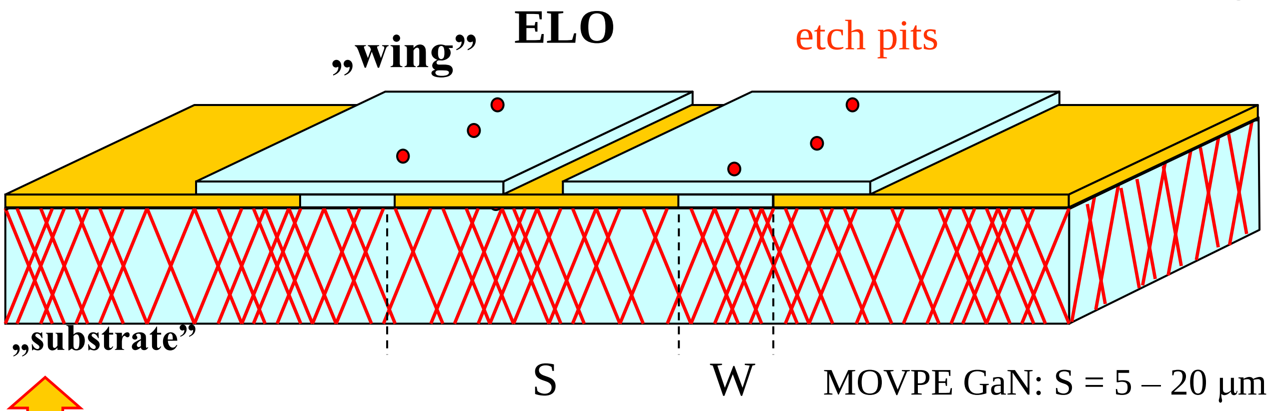
annealing

epitaxial lateral overgrowth - ELO

There are no universal method to reduce dislocation density in lattice mismatched heterostructures;
The best way is to avoid lattice mismatch – find the suitable substrate !!!

ELO = a method to reduce dislocation density in epitaxial structures

mask: SiO$_2$, Si$_3$N$_4$,
W, ZrN, grafit, ...



MOVPE GaN: S = 5 – 20 µm; W = 2 - 5 µm
LPE GaAs: S = 100 – 500 µm; W = 6 - 10 µm

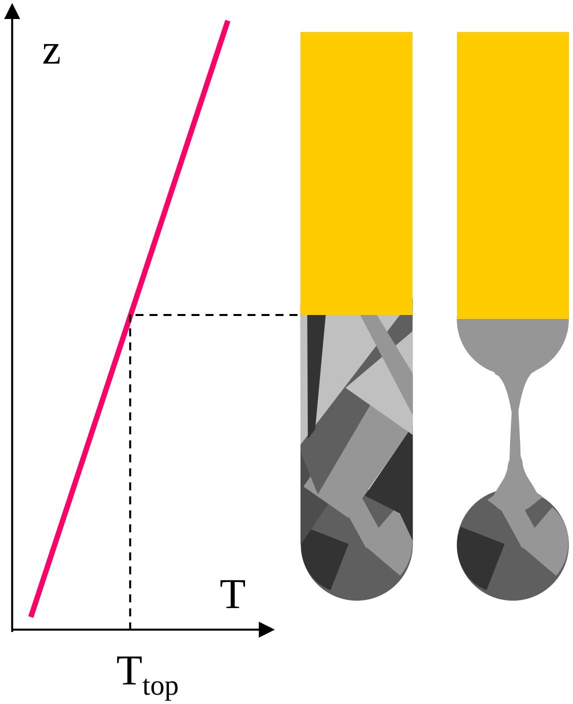
ELO	GaN	GaAs	A$_x$B$_{1-x}$C
buffer	GaN	GaAs	A$_x$B$_{1-x}$C
substrate	sapphire	Si	binary

new class of substrates with designed lattice parameter a = f(x)

wide and thin ELO layers needed

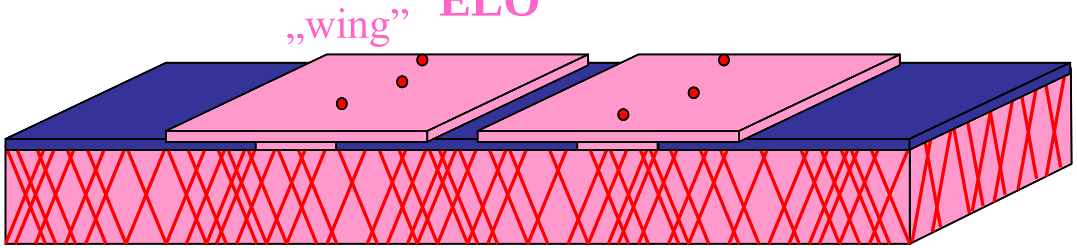
dislocation filtration in ELO – is it a new idea?

Necking in Bridgman growth



Cu crystal – Czochralski growth

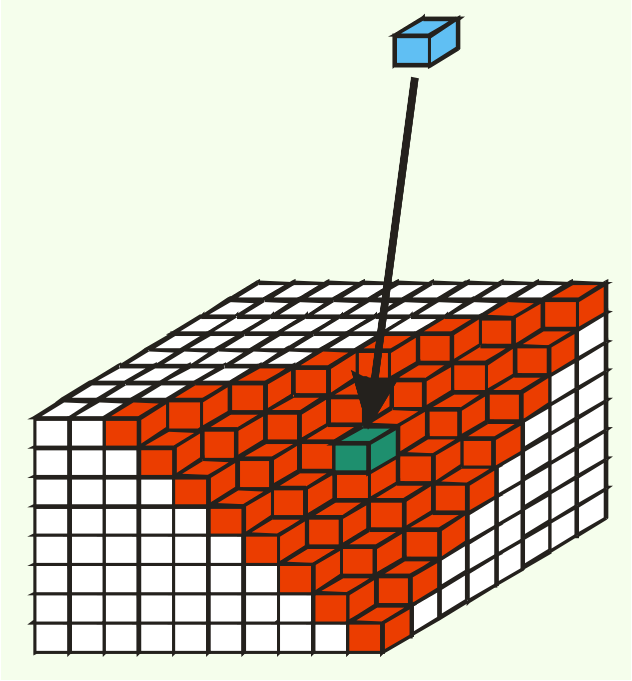
ELO

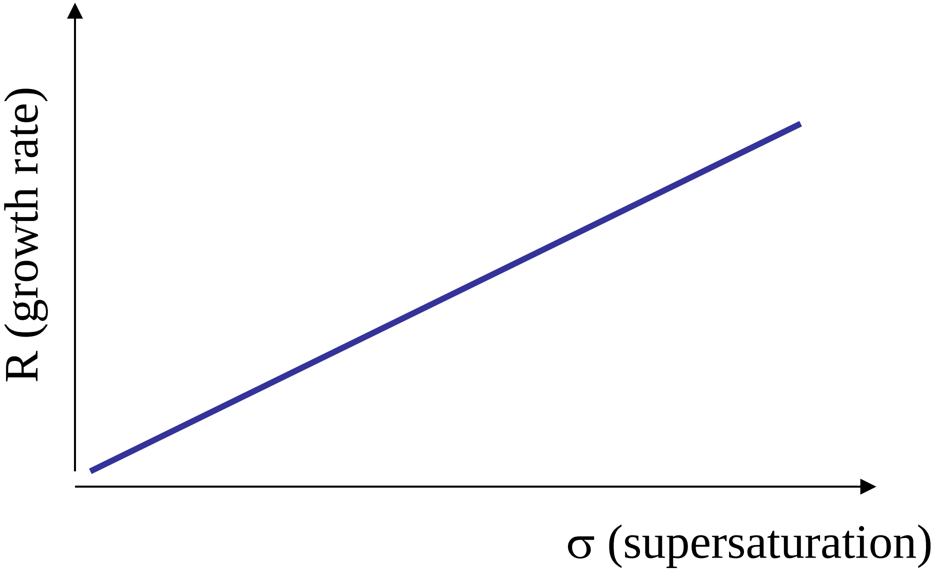


recipe: take from the seed info on crystal lattice; do not take defects;

Growth rate of various crystal faces (Krukowki's lecture)

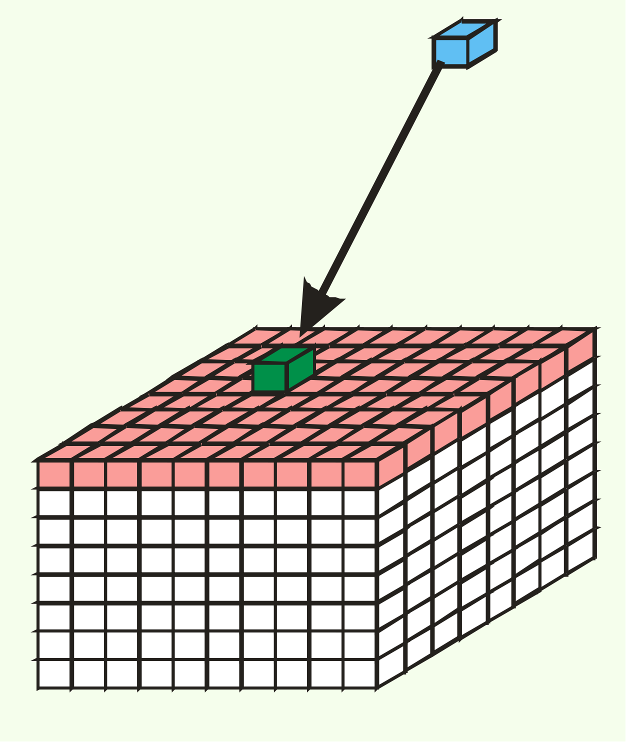
atomically rough surface

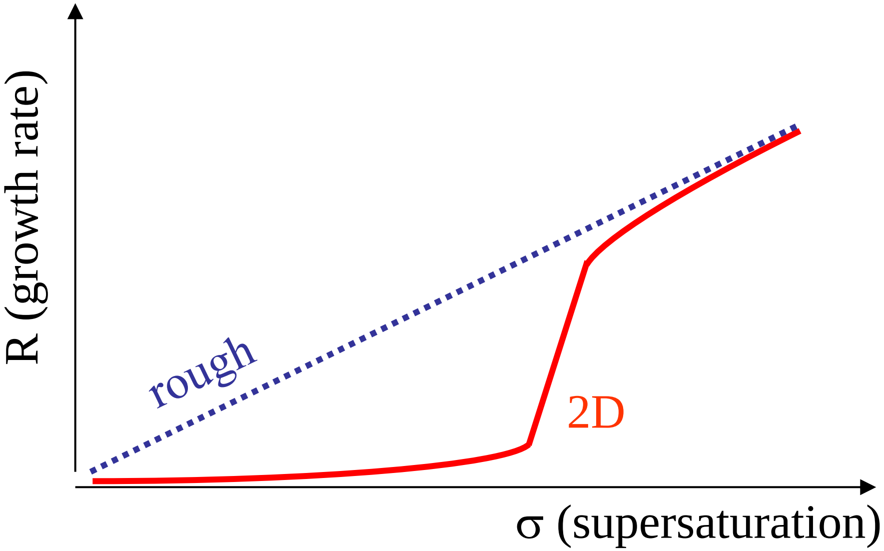




Growth rate of various crystal faces (Krukowki's lecture)

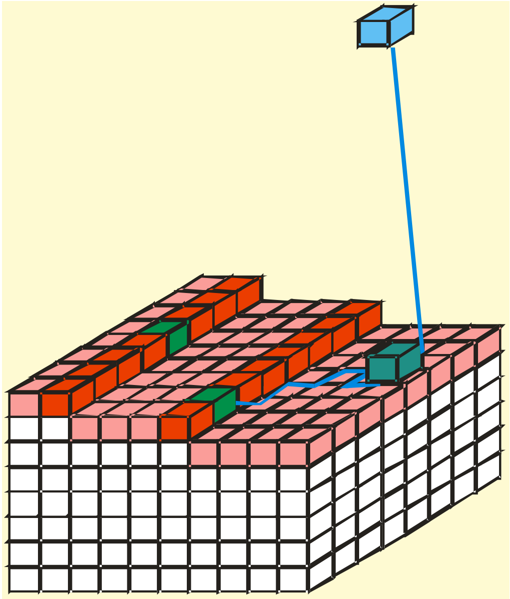
atomically smooth surface w/o dislocations (2D nucleation)

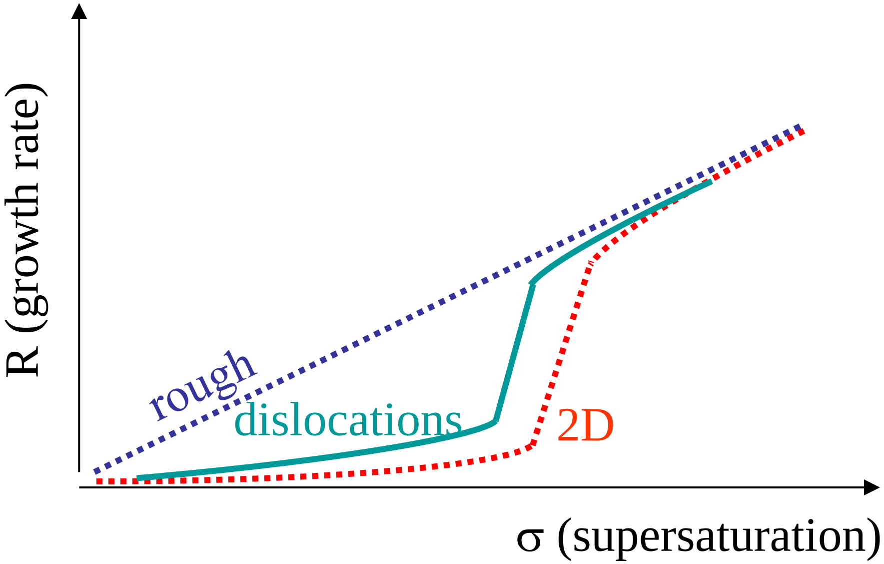




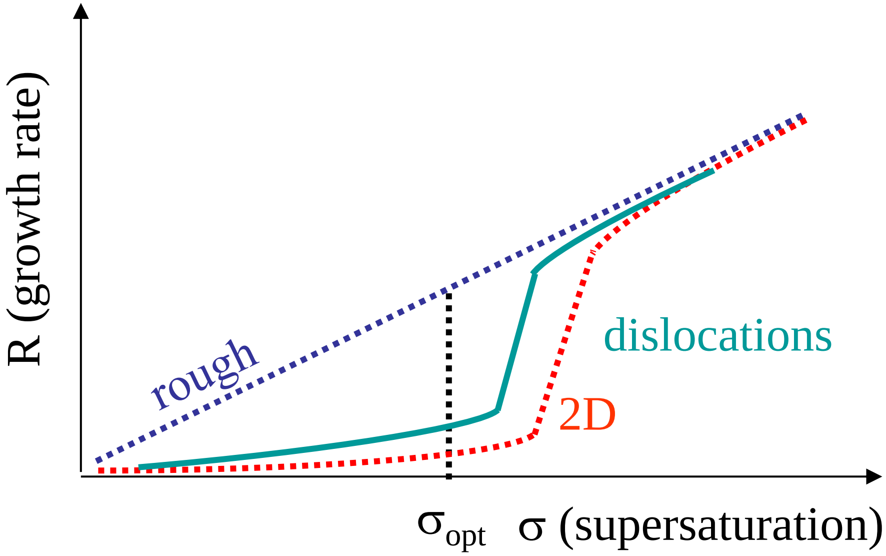
Growth rate of various crystal faces (Krukowki's lecture)

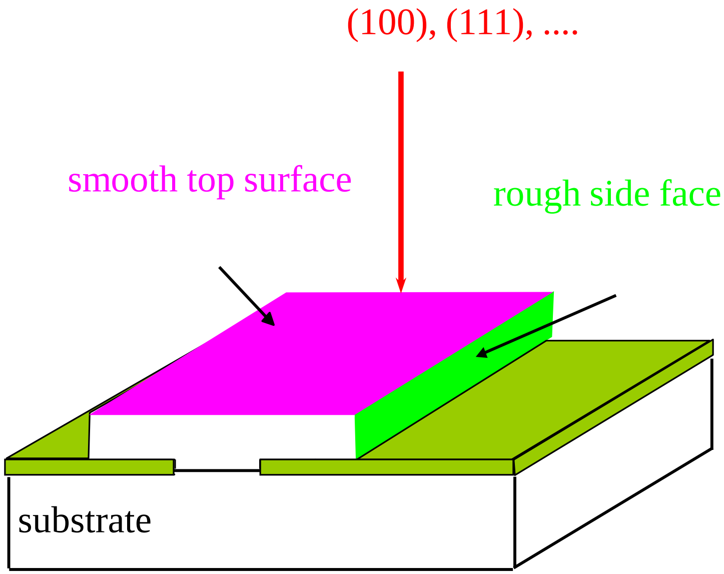
atomically smooth surface with dislocations





Mechanism of ELO growth





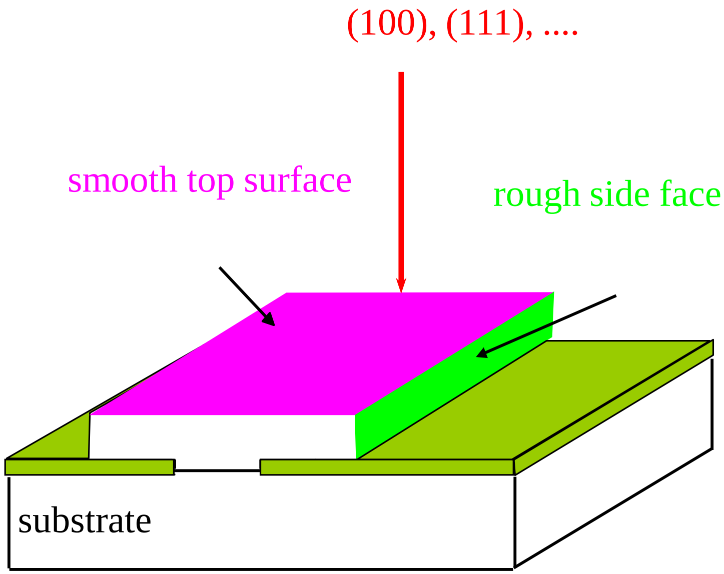
to get a high aspect ratio we need:

- **smooth top surface (low normal growth rate V_{ver})**
- **rough side face (high lateral growth rate V_{lat})**
- **adjust supersaturation to σ_{opt} - LPE perfect !!!**

- VPE, MOVPE, HVPE - possible

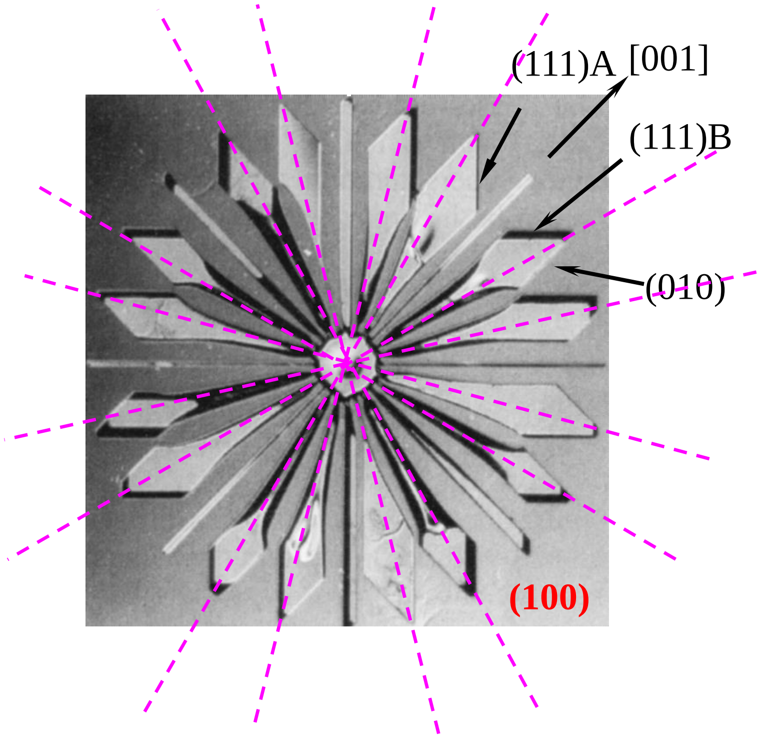
- MBE ???? problems

Mechanism of ELO growth



Zytkiewicz Cryst. Res. Technol. 1999

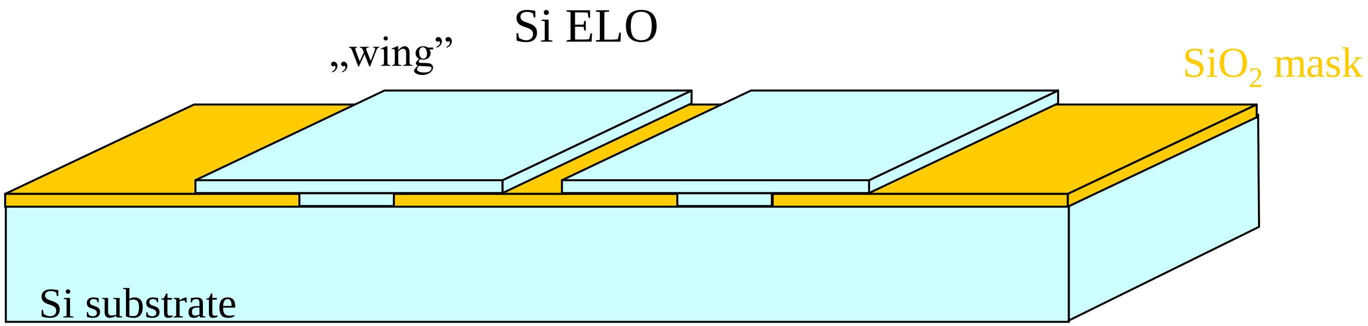
GaAs layer on (100) GaAs by LPE



8 equivalent window directions on substrate without miscut

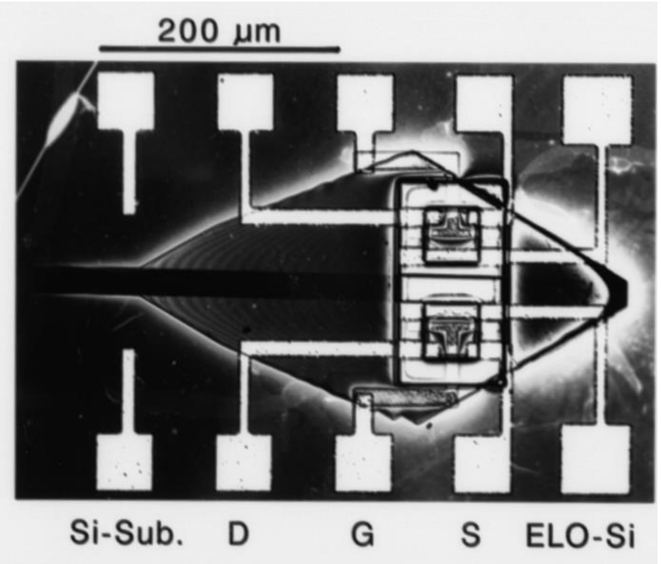
1 preferential window orientation on substrate with surface miscut

Application of ELO structures grown by LPE

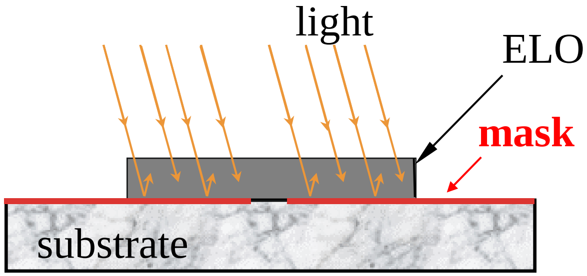


MOS transistor on ELO Si/SiO$_2$

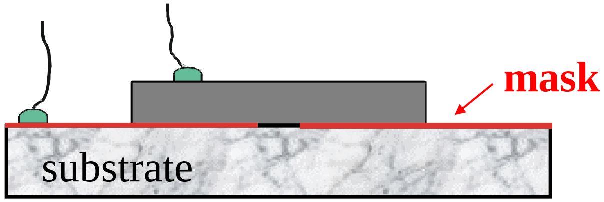
Bergmann et al. Appl. Phys. A (1992)



- silicon-on-insulator structures
- buried electrical contact/mirror

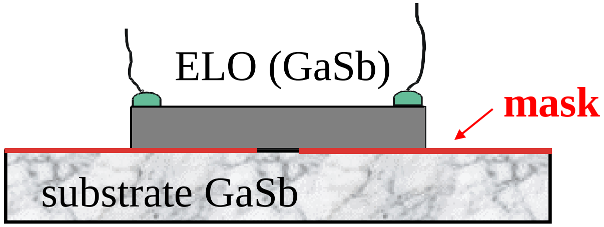


back mirror (photon recycling)



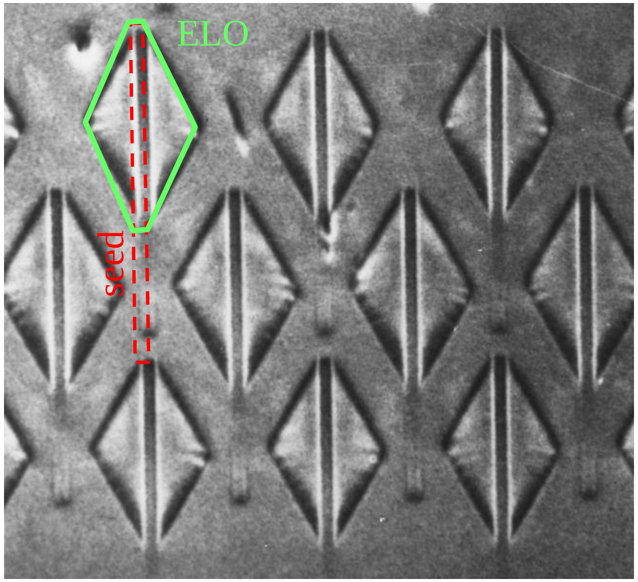
buried electrical contact

- electrical separation of epilayer from the substrate



ELO Si/SiO$_2$/Si by LPE

E. Bauser et al. Max-Planck Inst. Stuttgart



origin of strange ELO shape

- the case of dislocation-free Si substrate

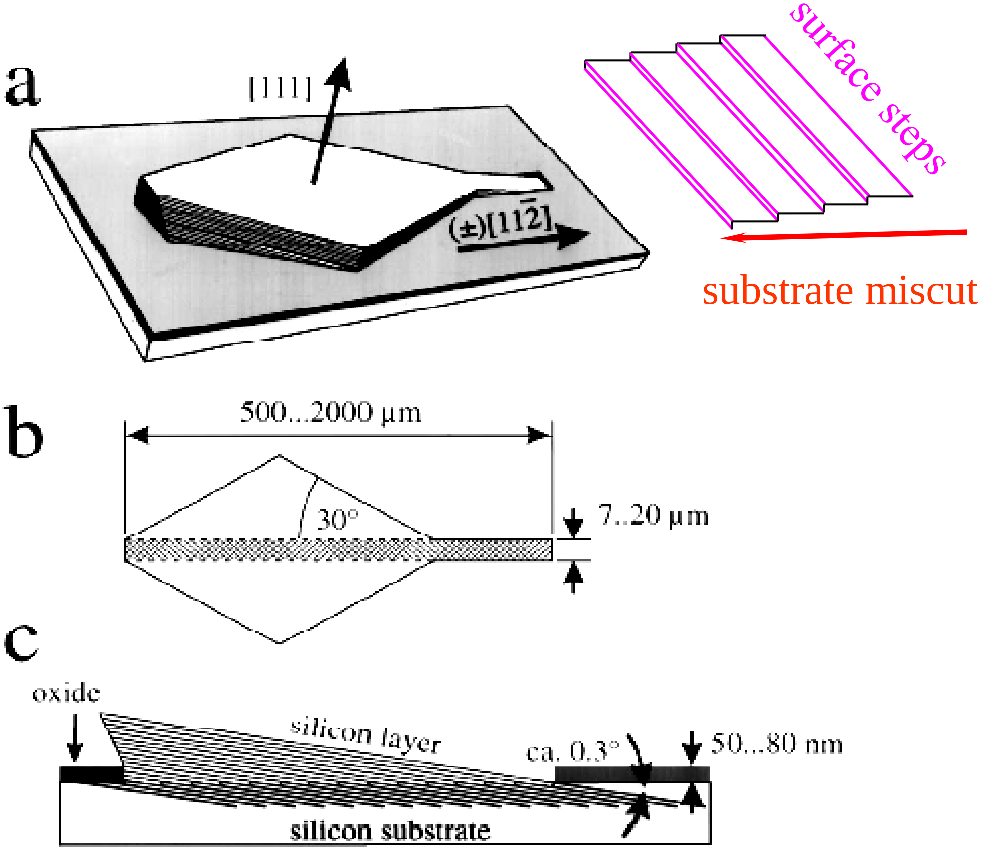
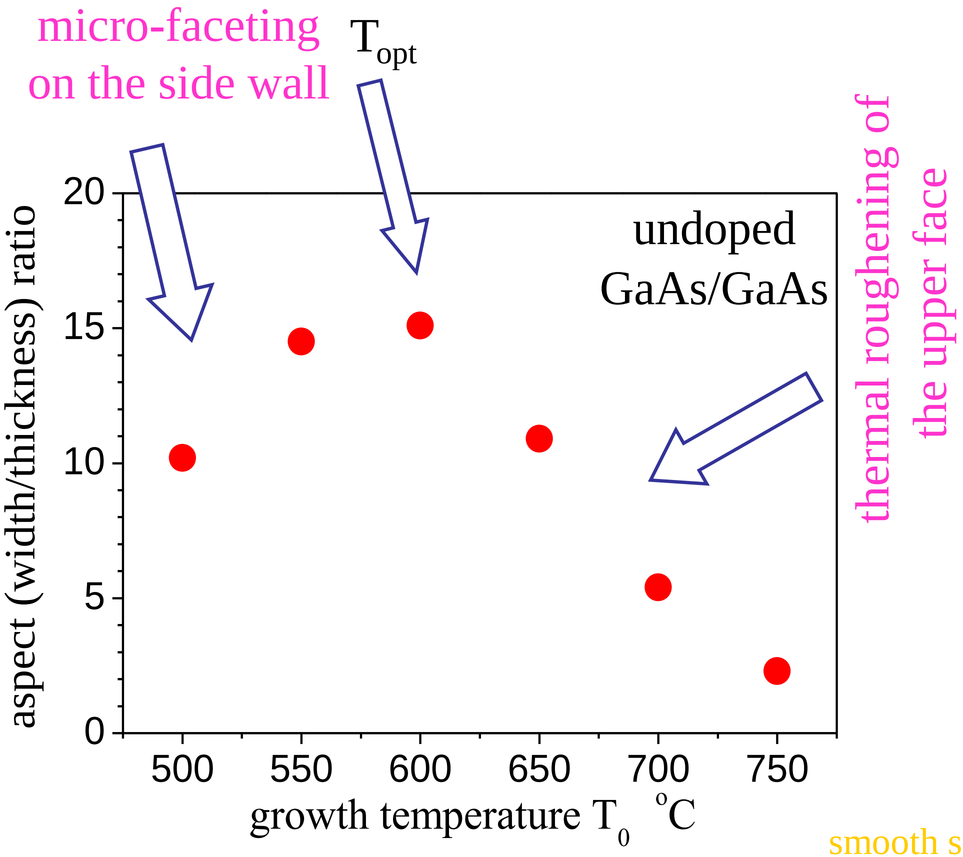


FIG. 1. Silicon layers grown from oxide-free seeding areas on {111} Si. Substrate partially masked by thermal oxide. Substrate off-orientation 0.3° in the [112] direction (schematic view). The crosshatched area in (b) indicates the seed window.

ELO – optimization of supersaturation in LPE

growth temperature

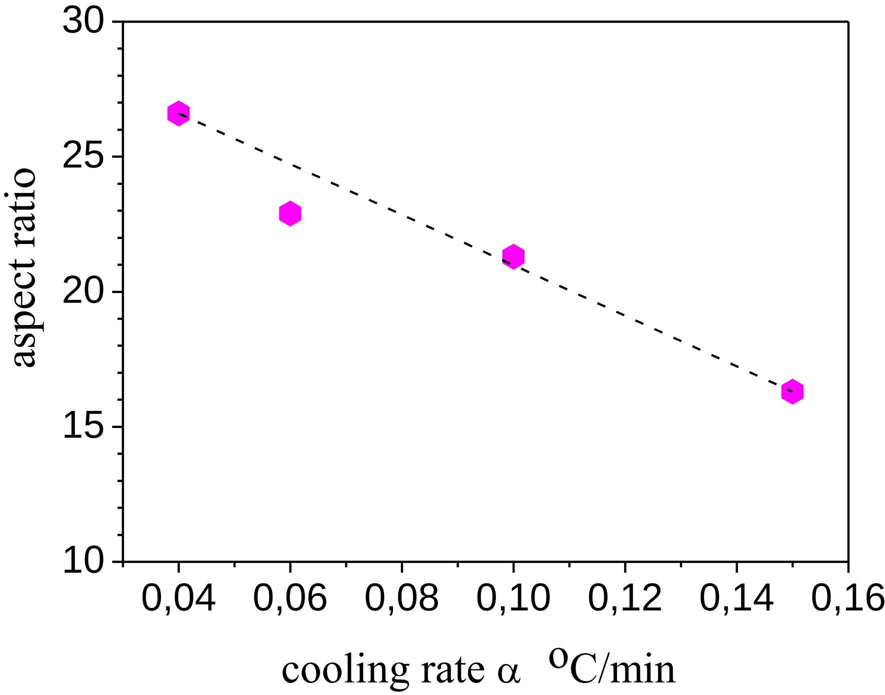


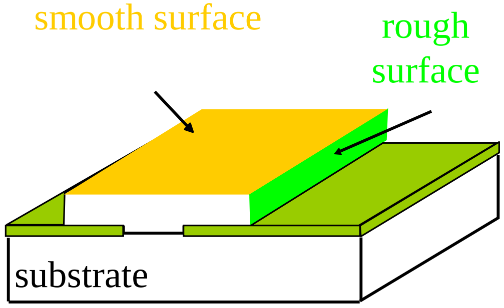
micro-faceting on the side wall

T_{opt}

thermal roughening of the upper face

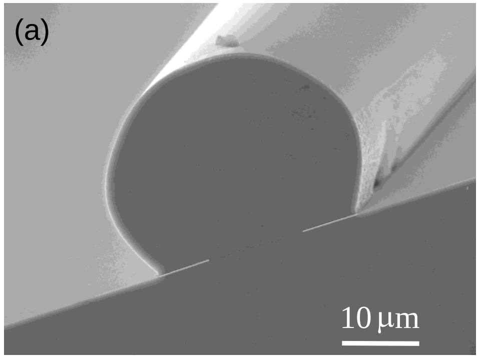
ELO GaAs - cooling rate



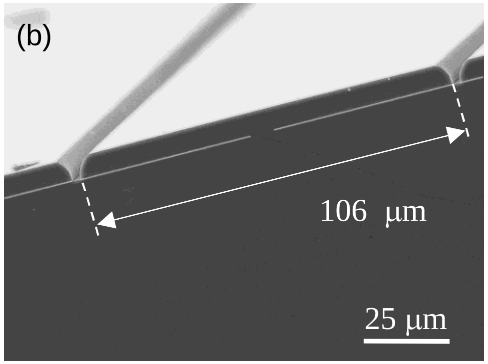


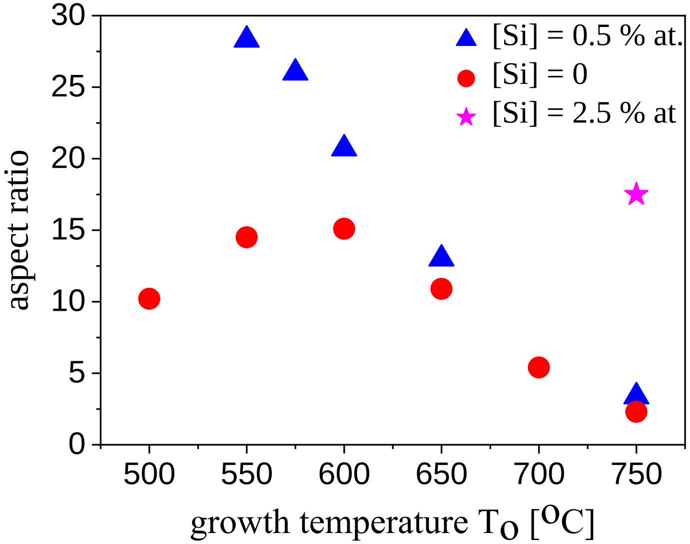
ELO – influence of doping on the aspect ratio (LPE)

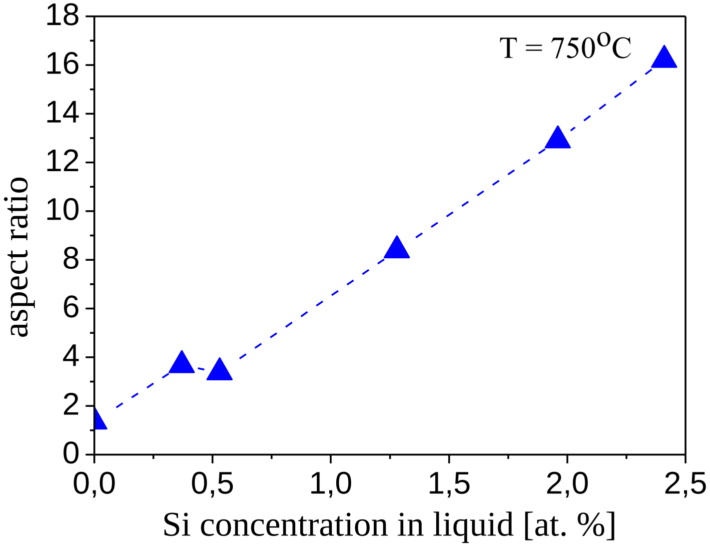
ELO GaAs - undoped

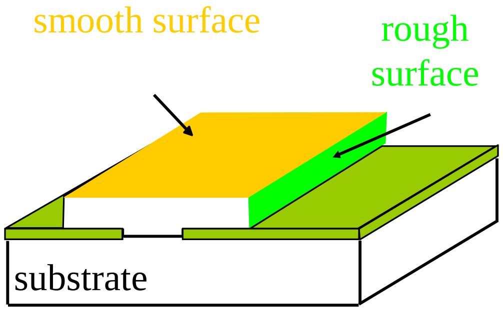


ELO GaAs - Si doped

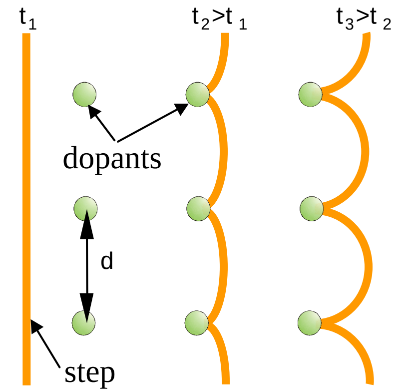








Model



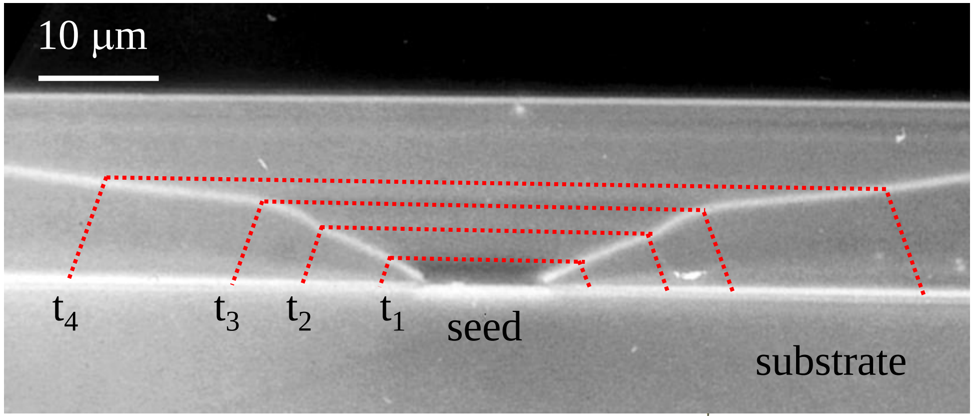
steps must squeeze between immobile impurities; flow of steps on upper surface slower

V_{ver} decreases V_{lat} increases

ELO by LPE – dopant incorporation

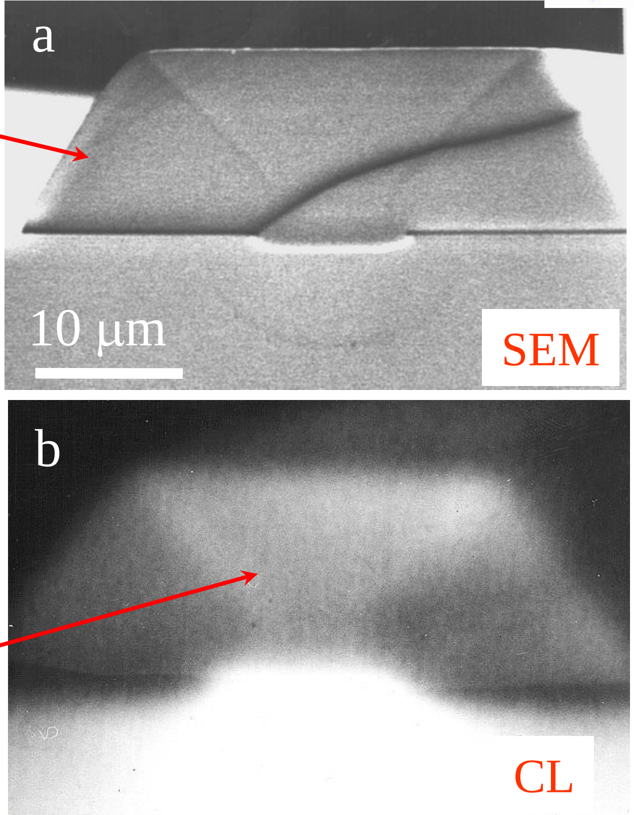
doping vs. growth rate ⇔ lecture by T. Słupiński

how ELO develops …

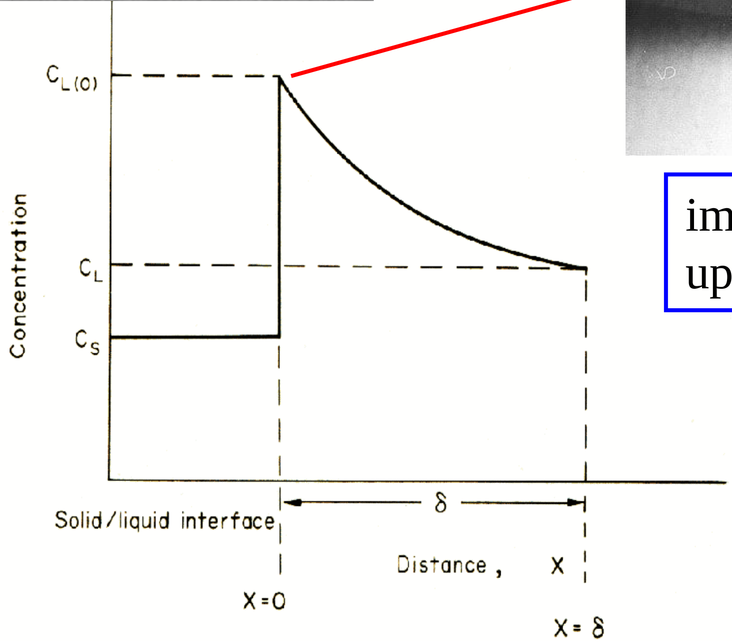


ELO GaAs:Te

rough face – no segregation k_0

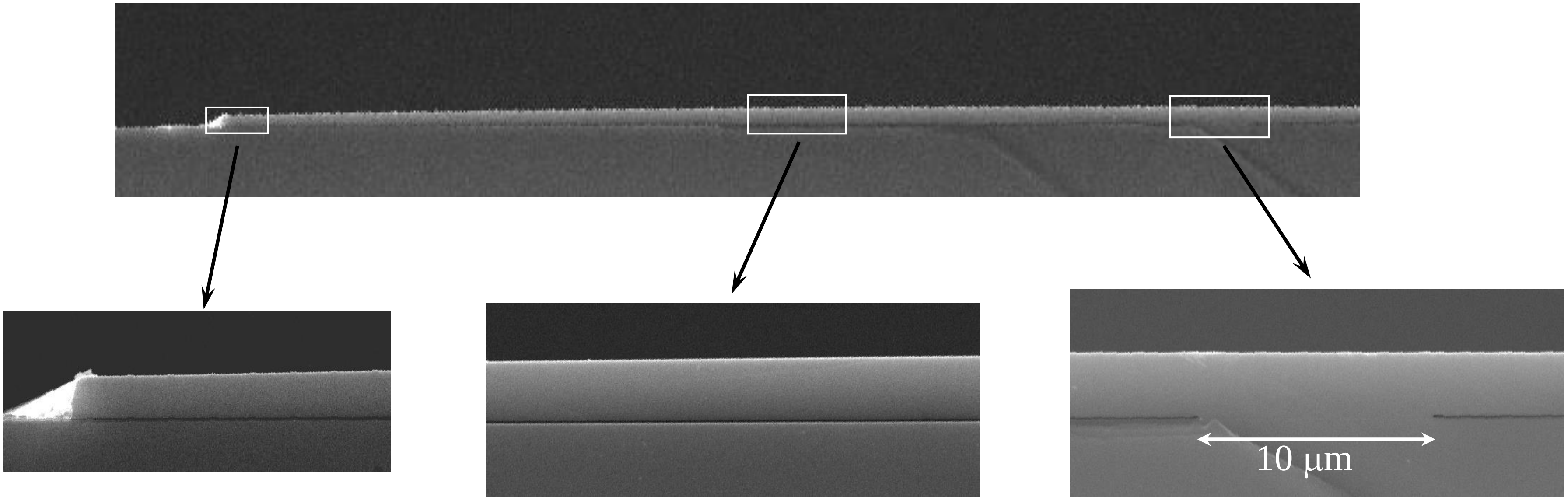


impurity segregation at upper face k_{eff}



GaAs ELO layers on GaAs substrates by LPE

L = 172 μm; t = 2.8 μm



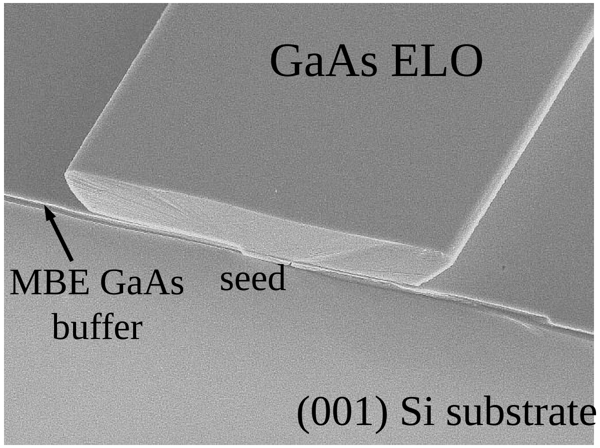
thickness t = 2.8 μm
width of the wing L = 172 μm

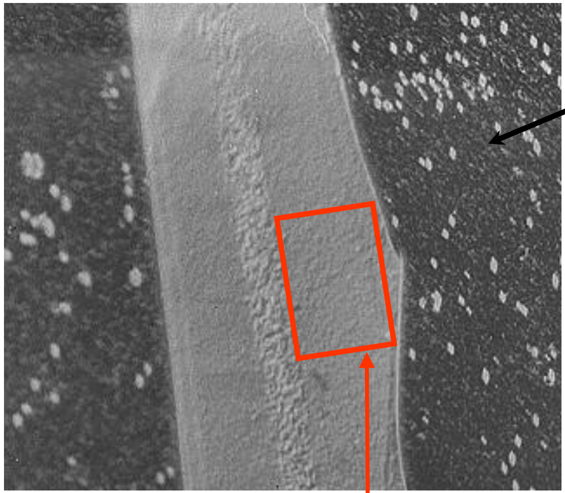
aspect ratio 2L/t = 126

Why the layer is thinner at the edge?
nonuniform growth …
bowing …

Filtration of dislocations in ELO - examples

LPE - GaAs/Si



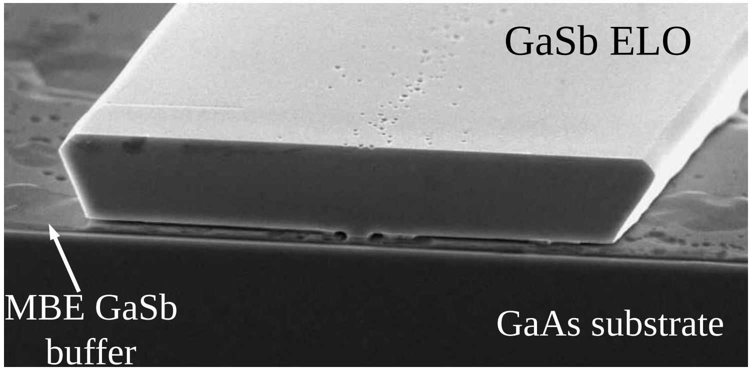


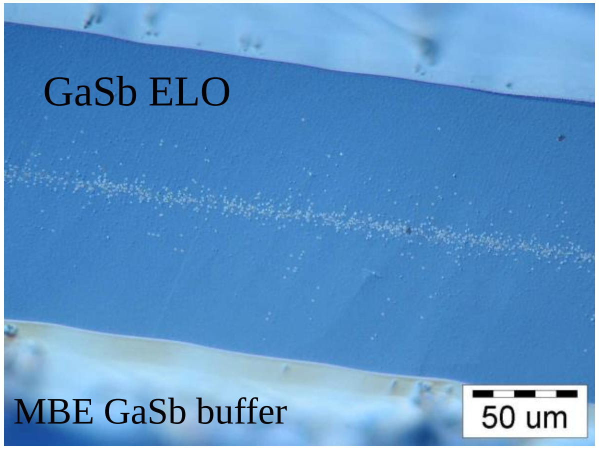
EPD > 10^{-8} cm^{-2}

device

after etching

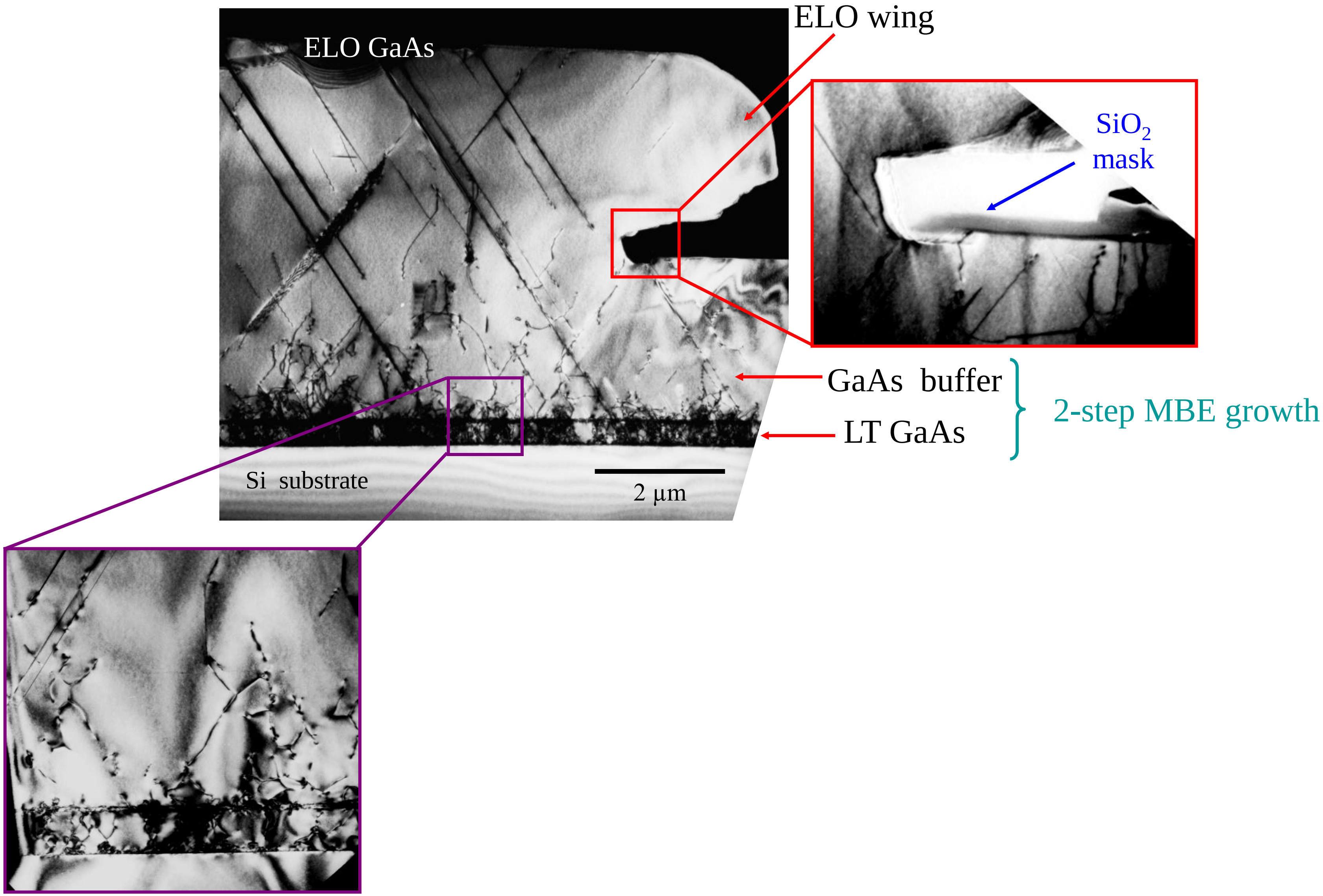
LPE - GaSb/GaAs





MBE grown GaAs/Si (GaSb/GaAs) templates; ELO by LPE

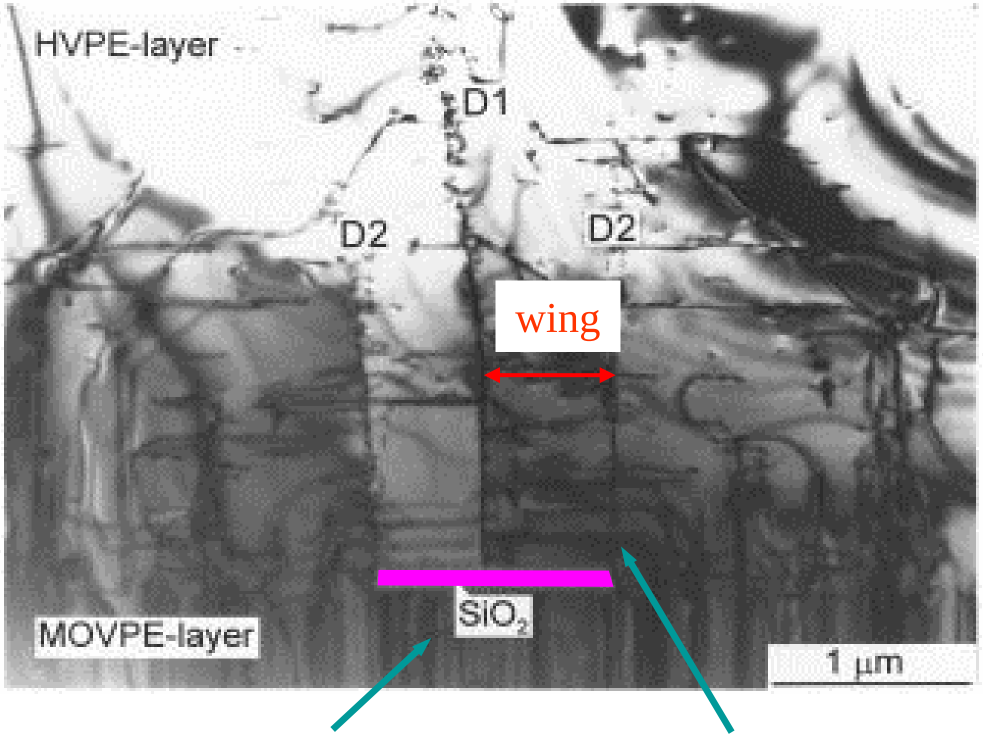
Filtration of dislocations in ELO: TEM of GaAs/Si



Filtration of dislocations in ELO: TEM of HVPE GaN/sapphire

Sakai et al. APL 1998

TEM



dislocations blocked
by the mask

bending of TD's
in the window area !!!

width of the ELO wing

	MOVPE GaN[*]	LPE GaAs/Si[**]	LPE GaAs/GaAs
wing width L	≤ 5 µm	≤ 90 µm	≤ 200 µm

[*] Fini et al. JCG (2000) [**] Chang et al. JCG (1998)

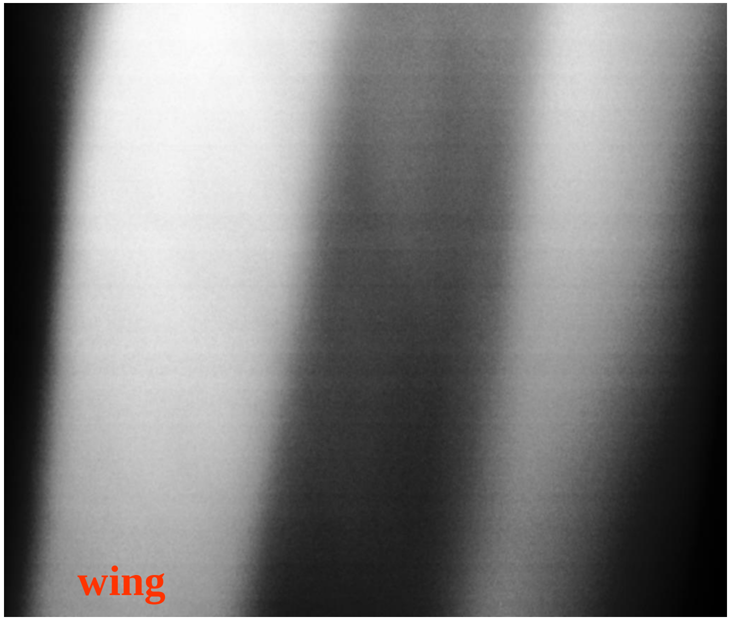
Filtration of dislocations in ELO: cathodoluminescence

Zytkiewicz Thin Solid Films 412 (2002) 64

Yu et al. MRS Internet Nitride Semicond. Res. 1998

LPE GaAs/Si

integrated CL

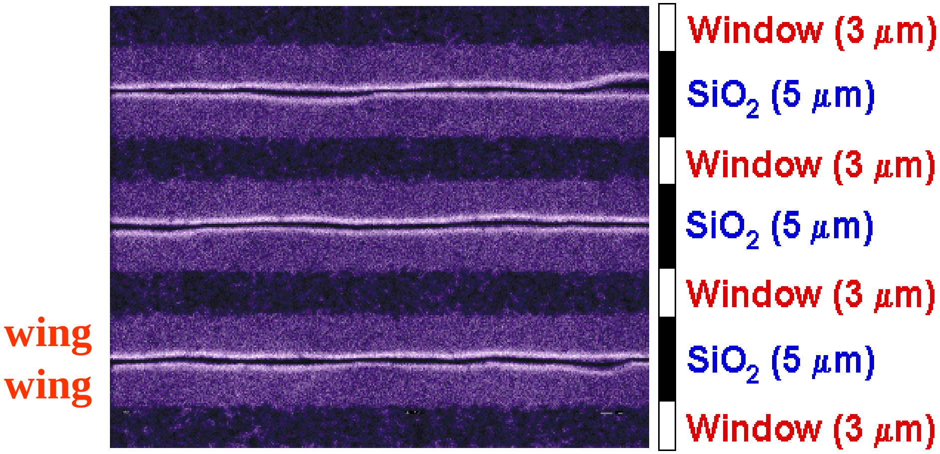


↑

GaAs grown over the seed

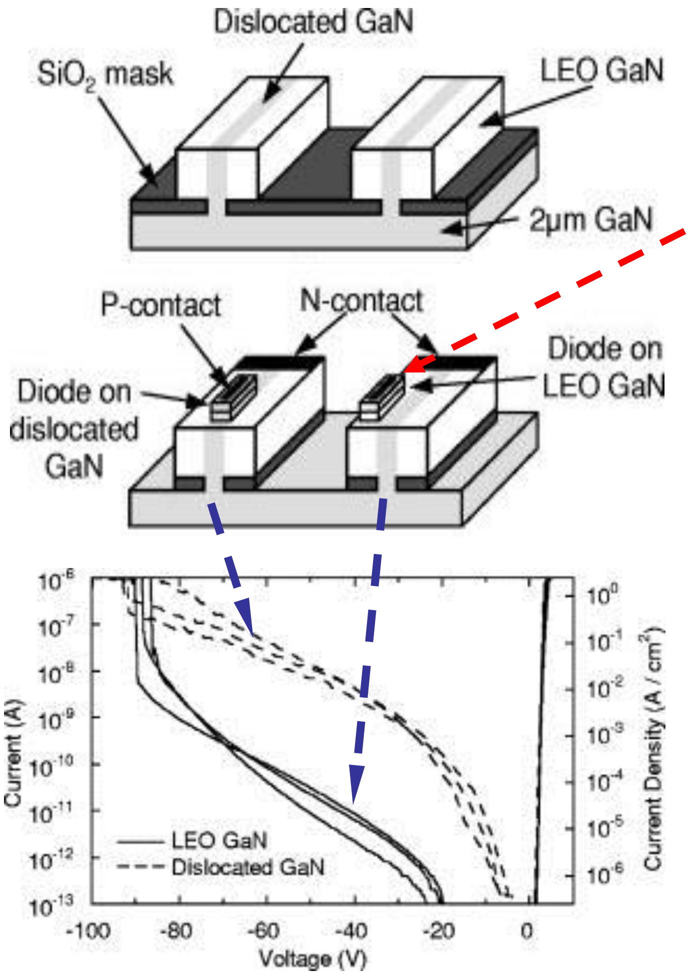
MOVPE GaN on sapphire

band edge emission 365 nm



ELO structures for devices

Kozodoy et al. APL 1998

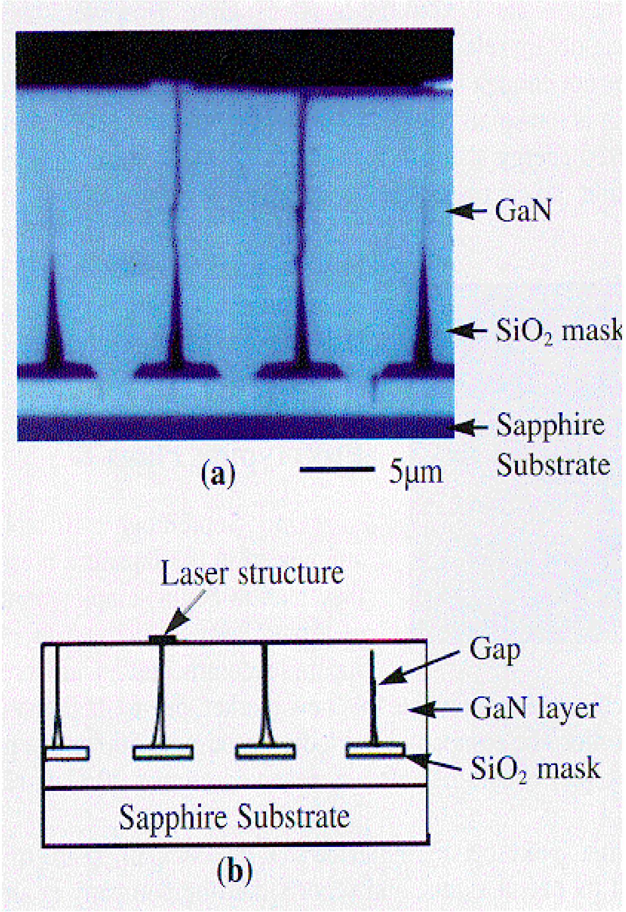


!!!

large leakage current due to TD

Semicond. Res. 4S1, G1.1 (1999)

CW RT blue LD - Nichia



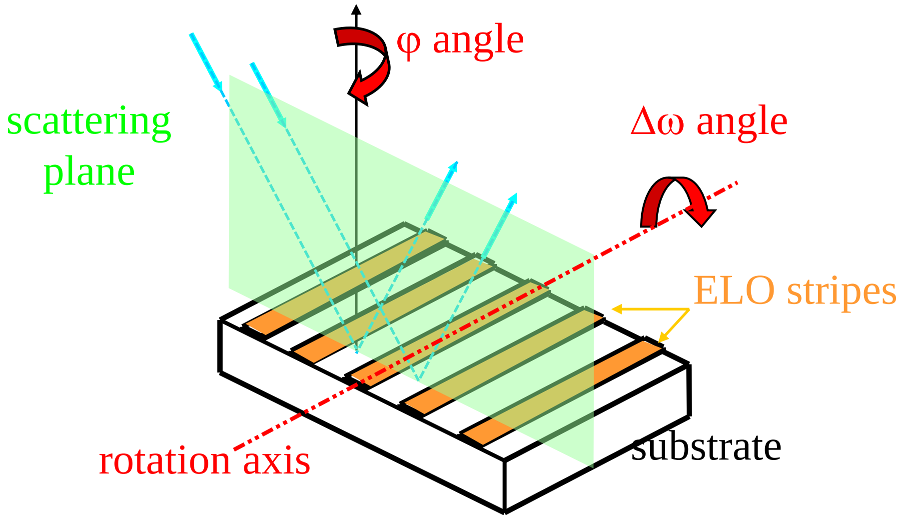
on the wing $j_{th} = 3$ kA/cm^2

on the window $j_{th} = 6$-9 kA/cm^2

Strain in ELO layers

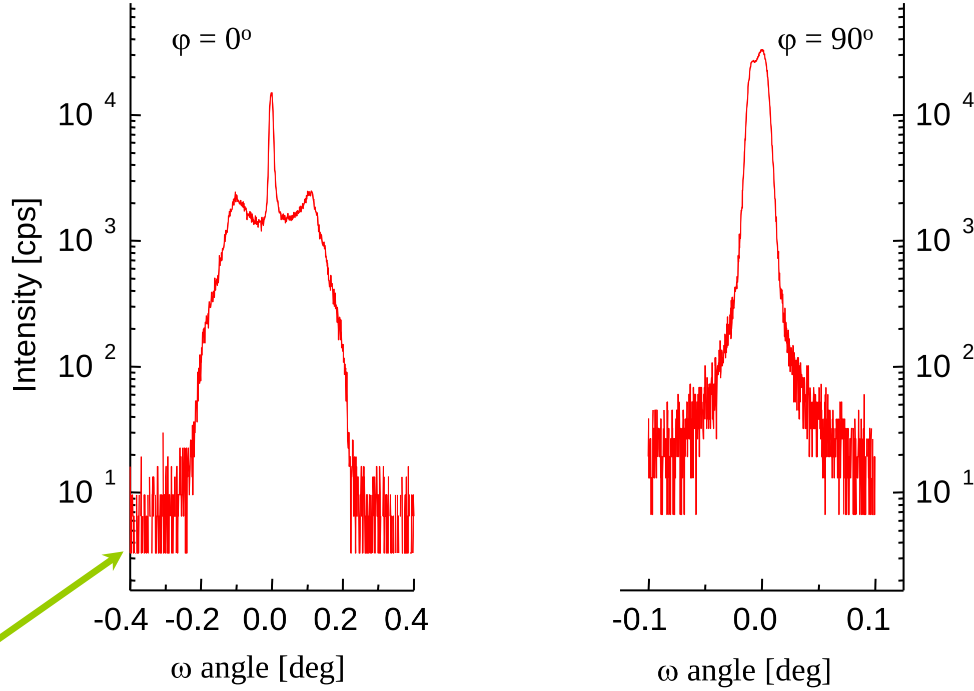
XRD – lecture by M. Leszczyński

XRD geometry



ELO GaAs on SiO_2-coated GaAs

Zytkiewicz et al. JAP 1998

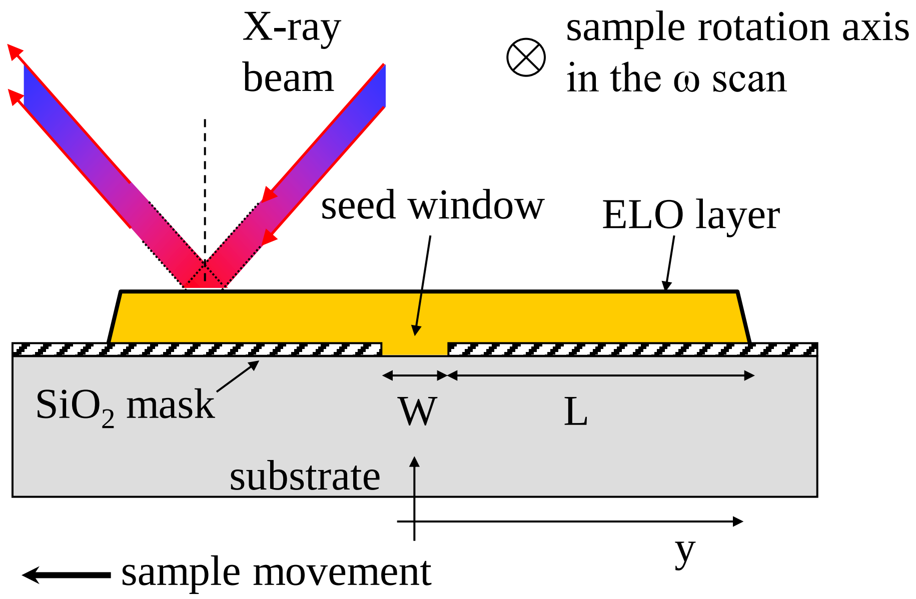


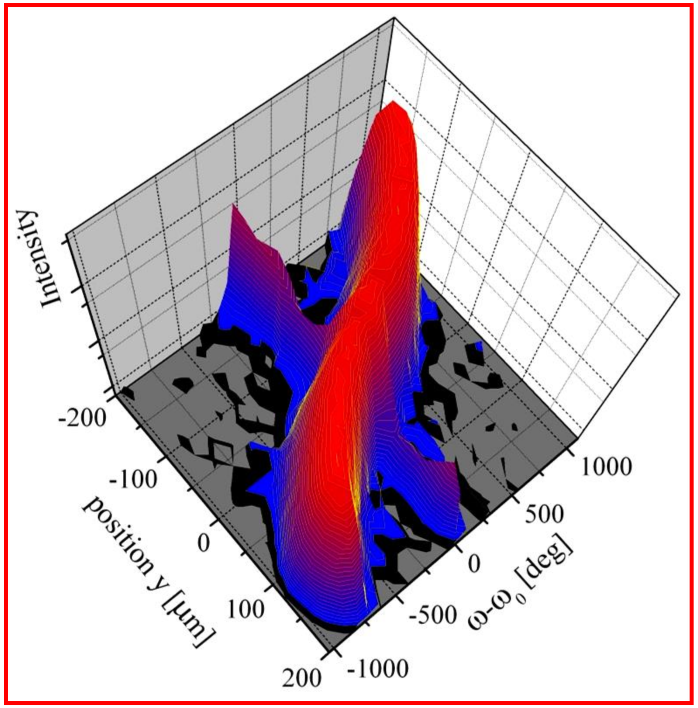
broadening of the RC:

- different values of lattice parameters ?
- different orientations of the ELO stripes ?
- bowing – direction ?

“typical” GaAs epilayer

Strain in ELO layers – local XRD

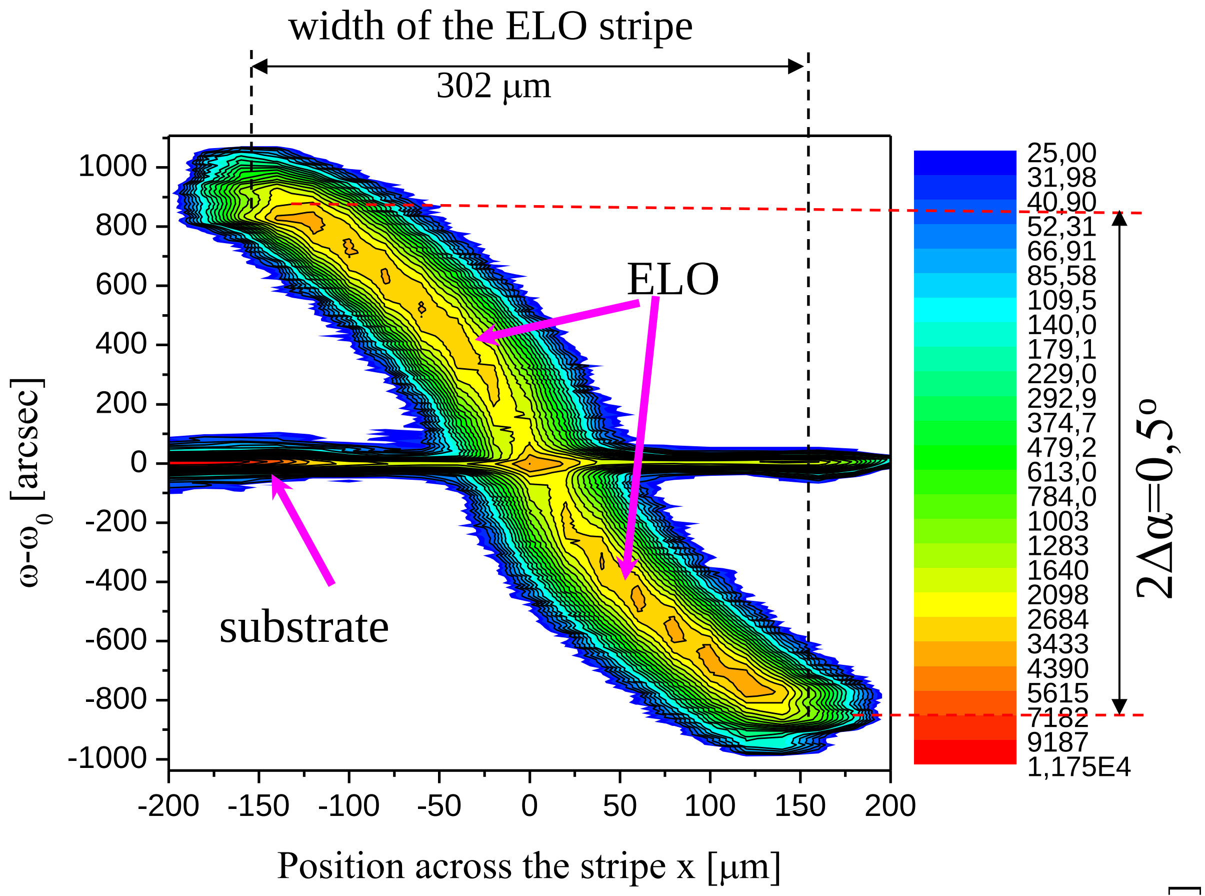


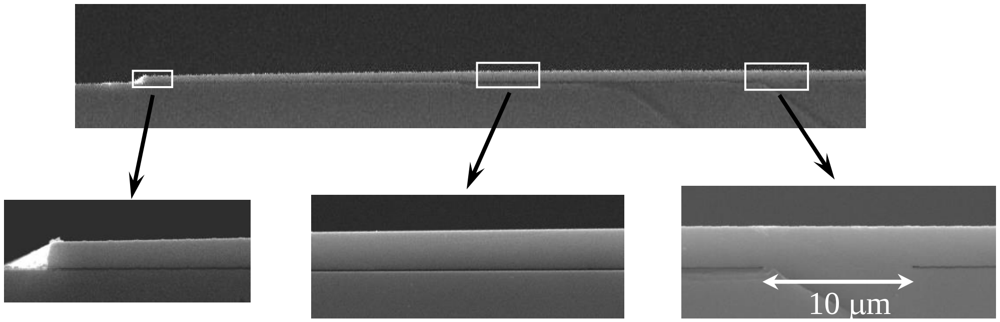


X-ray beam 5 – 10 µm × 0.5 – 10 mm
sample movement step 5 – 20 µm
RC, RSM, … measured *locally* → Rocking Curve mapping

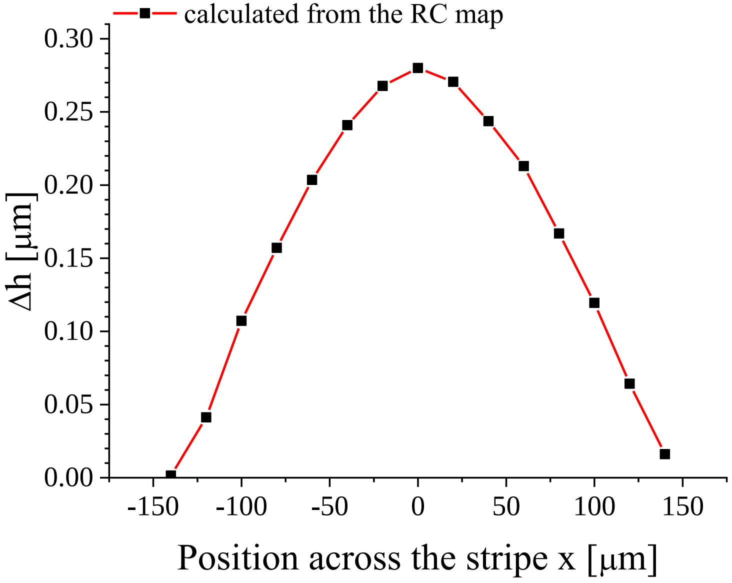
Strain in ELO layers – local XRD

Czyzak et al. Appl. Phys. A 2008



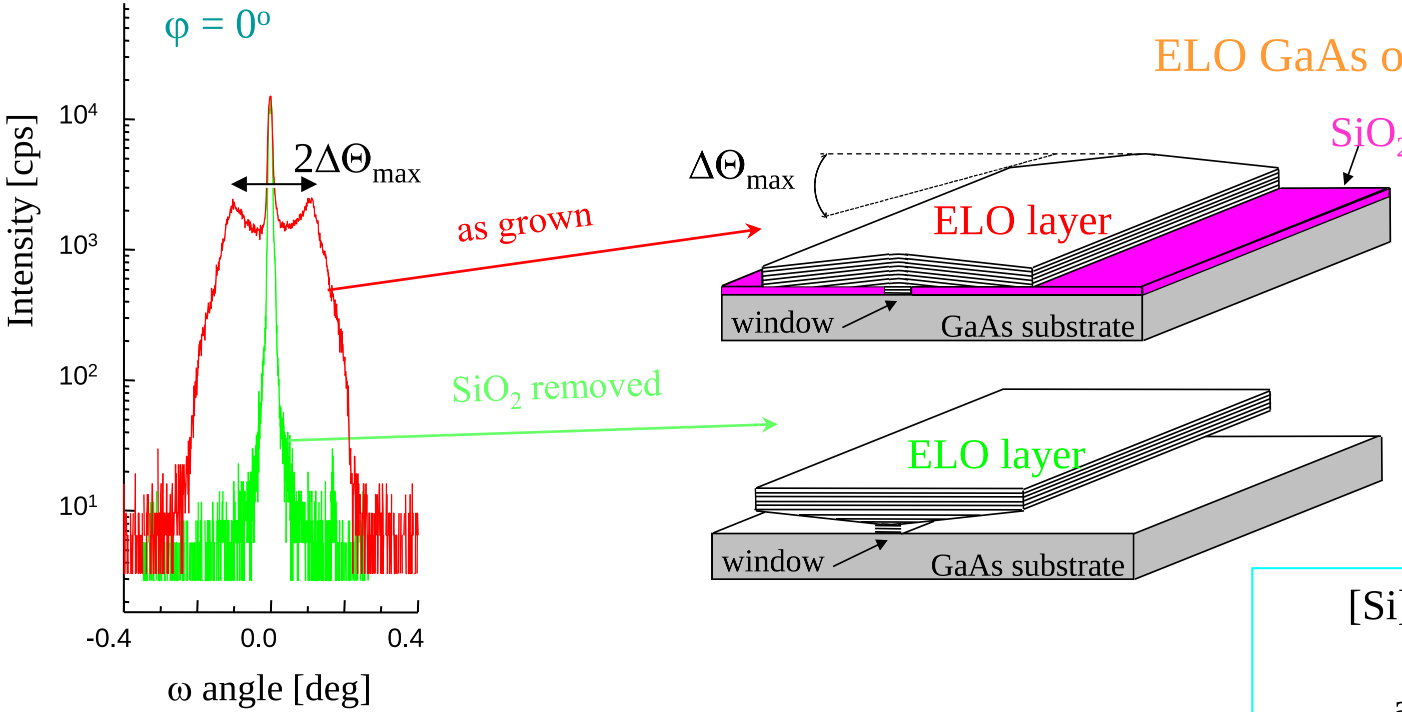


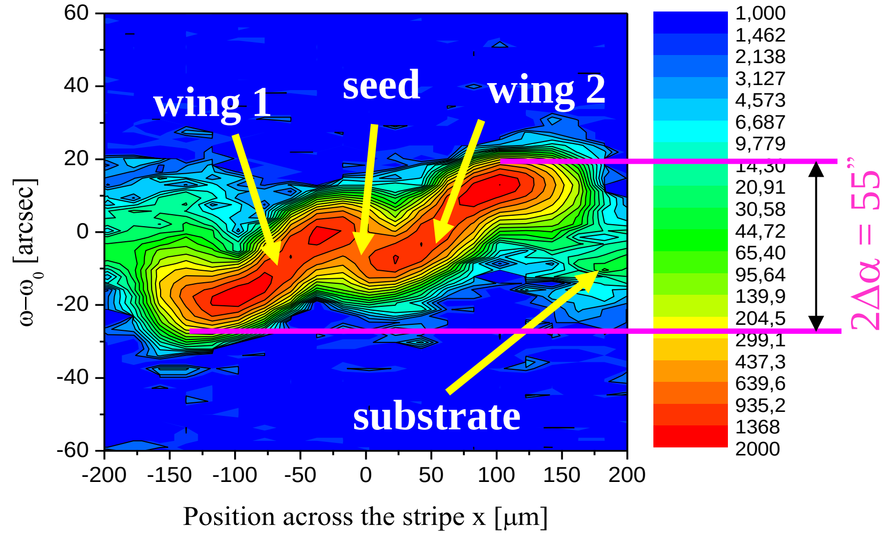
shape of (001) GaAs planes



Bending of ELO layers

ELO GaAs on SiO_2-coated GaAs





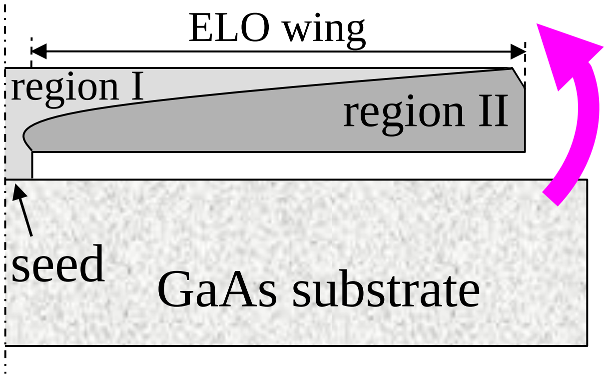
$[Si]^{region\ I} > [Si]^{region\ II}$

↓

$a_{region\ I} < a_{region\ II}$

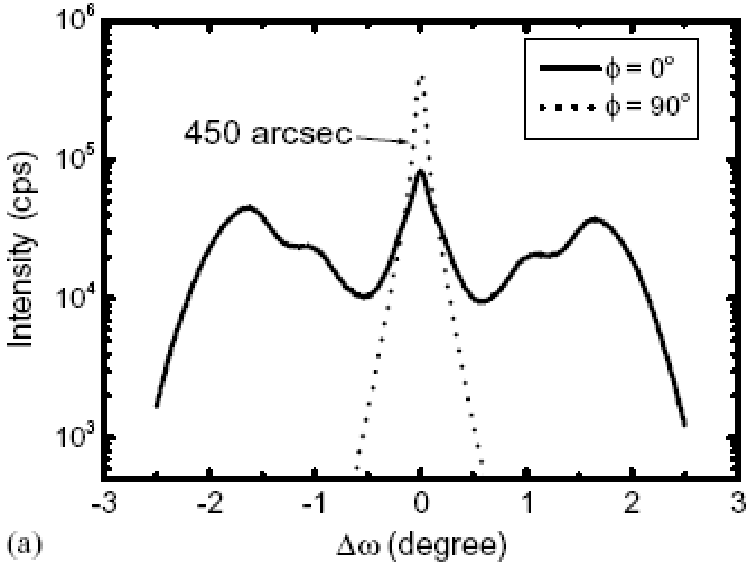
↓

upwards bending of the wing



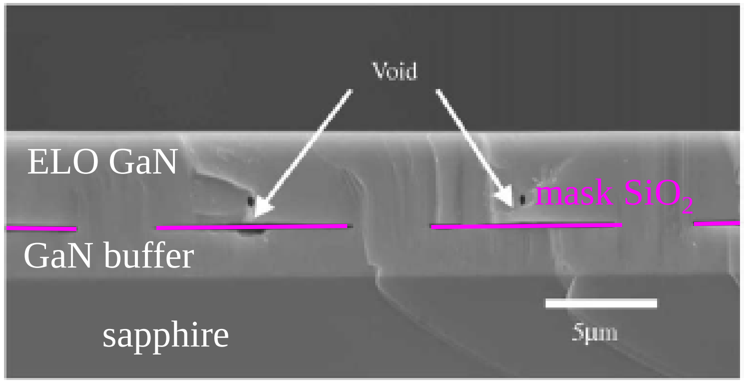
Residual bowing due to nonuniform doping

Bending of ELO layers – common in ELO (GaN, Si, GaAs, etc.)



ELO GaN on sapphire

Kim et al. JCG 2002



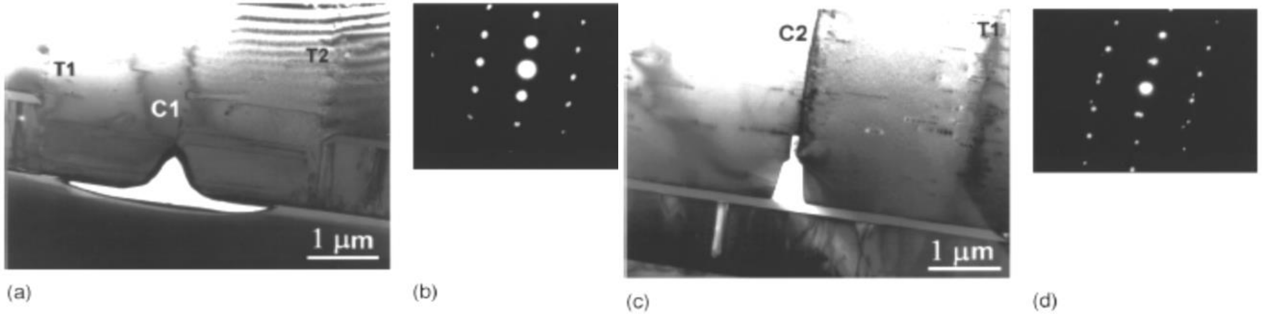
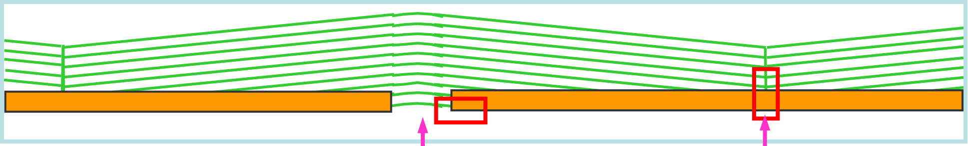


FIG. 2. TEM cross-section images and electron diffraction patterns taken from (a) and (b) window and (c) and (d) mask region.

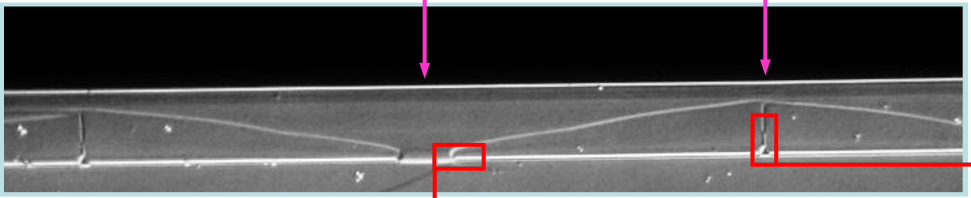
- tilt angle and tilt direction from electron diffraction in TEM
- synchrotron XRD

Coalescence of ELO stripes

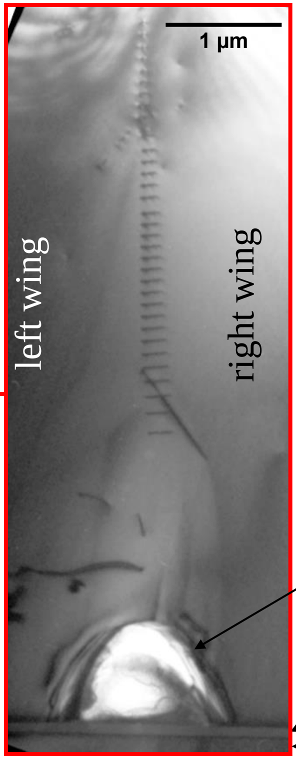


growth window

front of coalescence



low angle grain boundary

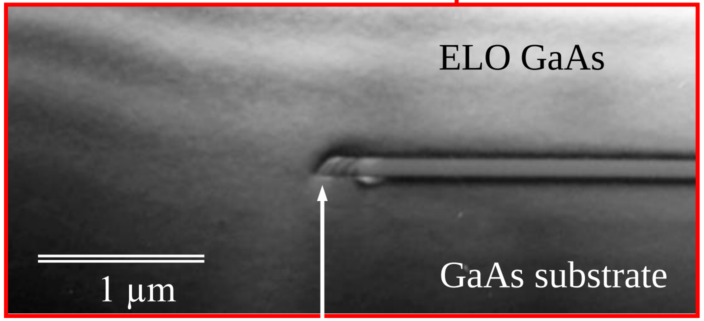


Zytkiewicz et al. JAP 2007

void

SiO_2 mask

GaAs substrate



no dislocations
above the mask edge

Similar effect in:

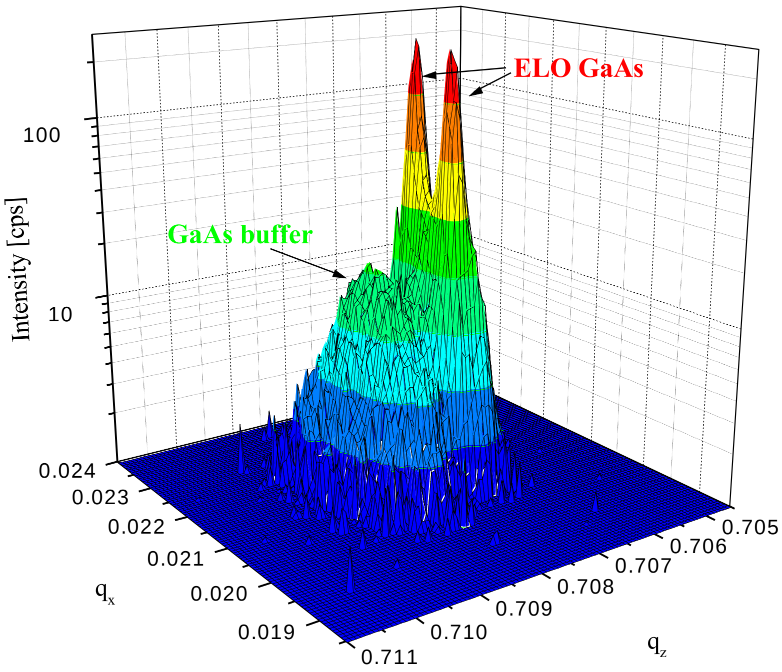
ELO Si on Si - Banhart et al. Appl. Phys. 1993

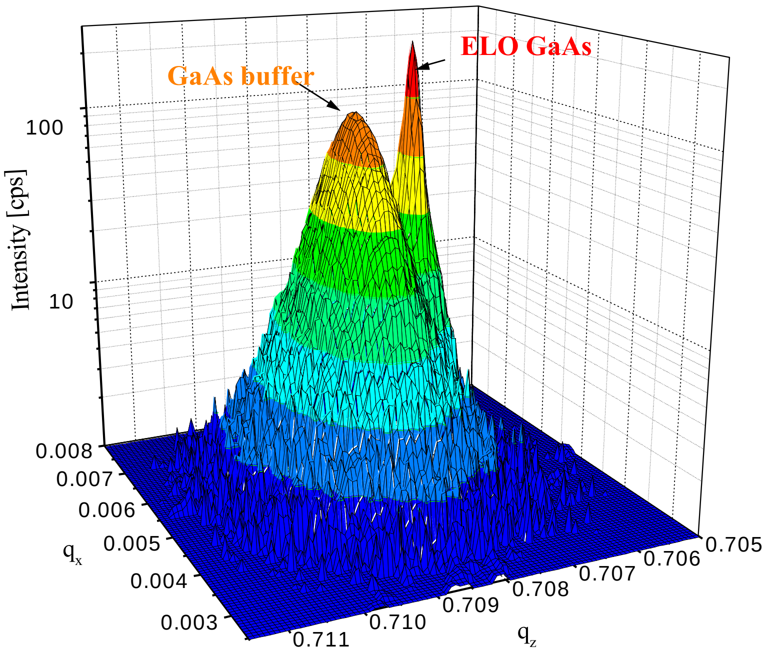
ELO GaN on sapphire - Sakai et al. APL 1998

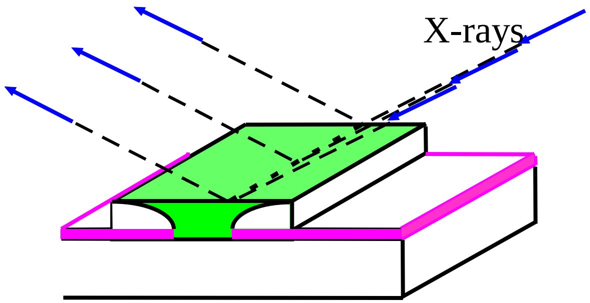
PE GaN on sapphire - Chen et al. APL 1999

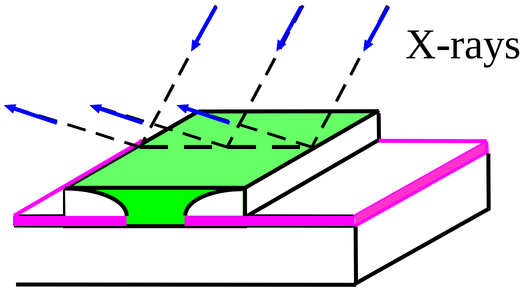
.....

Thermal strain in ELO structures (GaAs/SiO$_2$/GaAs/Si)









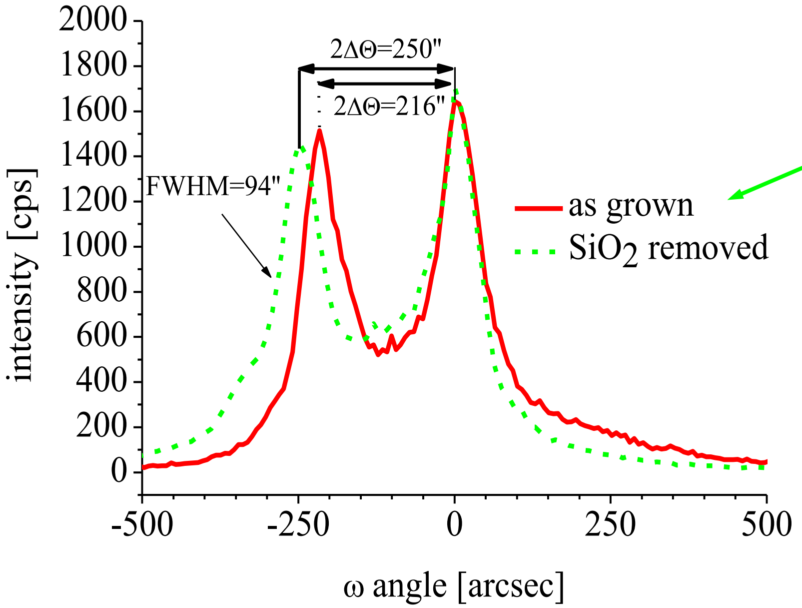
Thermal strain in ELO structures (GaAs/SiO$_2$/GaAs/Si)

Zytkiewicz et al. APL 1999

Our model:

ELO GaAs/Si:

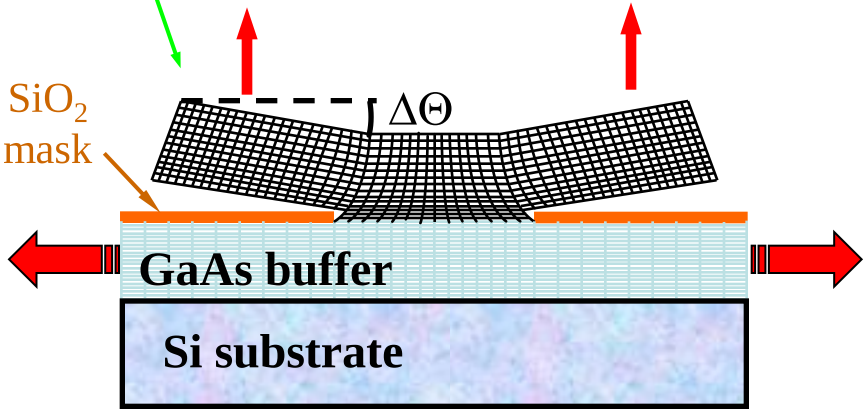
- wings hanging over the SiO$_2$ mask (no mask-induced tilt)
- wings tilted upwards



direction of tilt ⟷ sign of thermal strain in the buffer

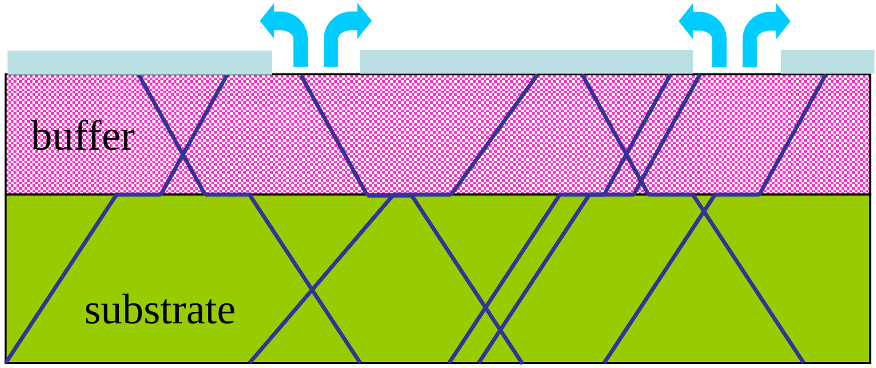
GaAs/Si	GaN/sapphire
$\alpha_{GaAs} > \alpha_{Si}$	$\alpha_{GaN} < \alpha_{sapphire}$
tension in GaAs buffer	compression in GaN buffer
upwards tilt	downwards tilt

Fini et al. Appl. Phys. Lett. 2000

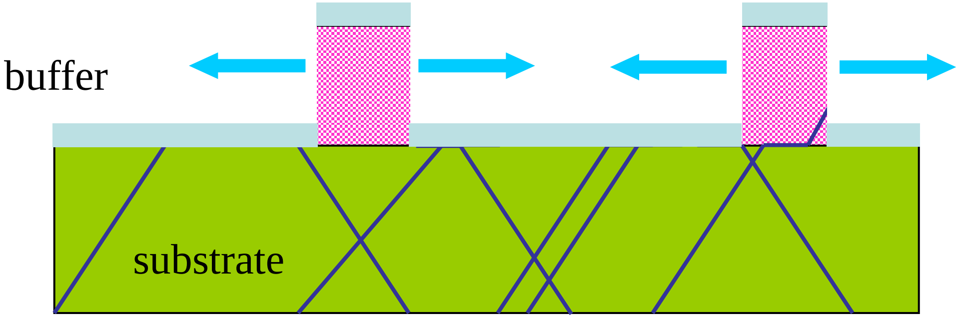


Another ELO concepts (e.g. Pendeo-epitaxy)

Epitaxial Lateral Overgrowth



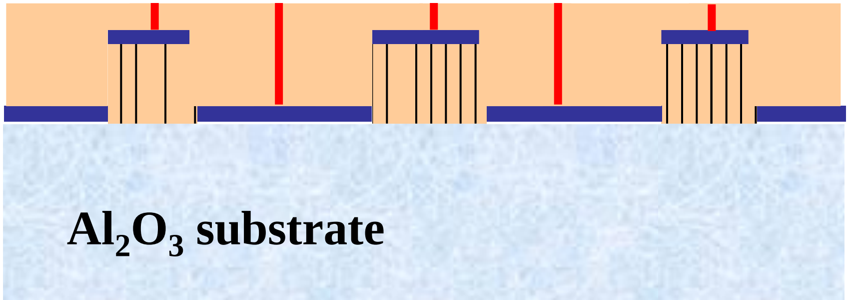
New concept



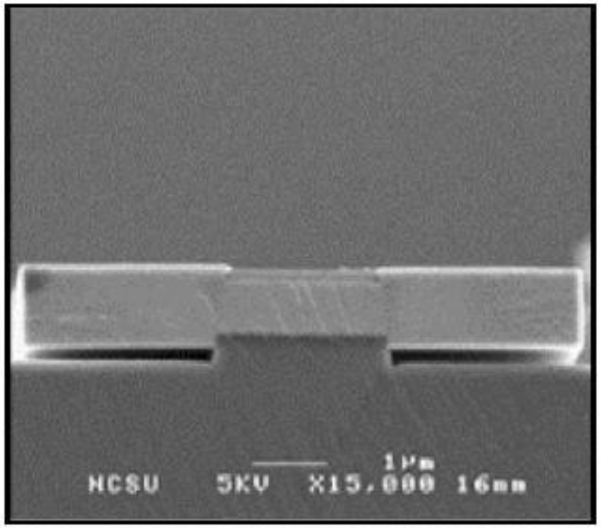
Pendeo-epitaxy

pendeo - “hanging on”
“suspending from”

™ Nitronex Corp., Raileigh,
North Caroline University



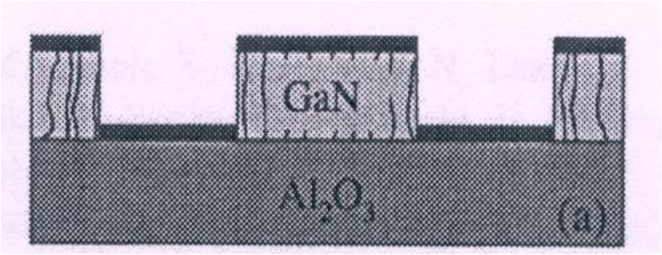
Davis et al. JCG 2001

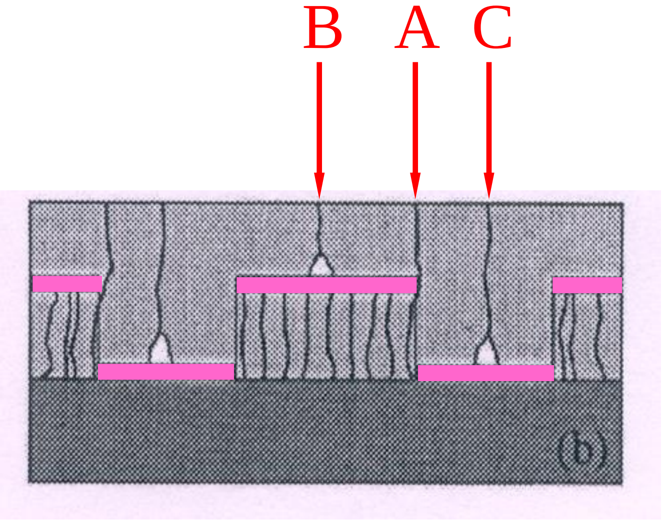


PE vs. ELO: reduction of TD density over the whole wafer within one PE process

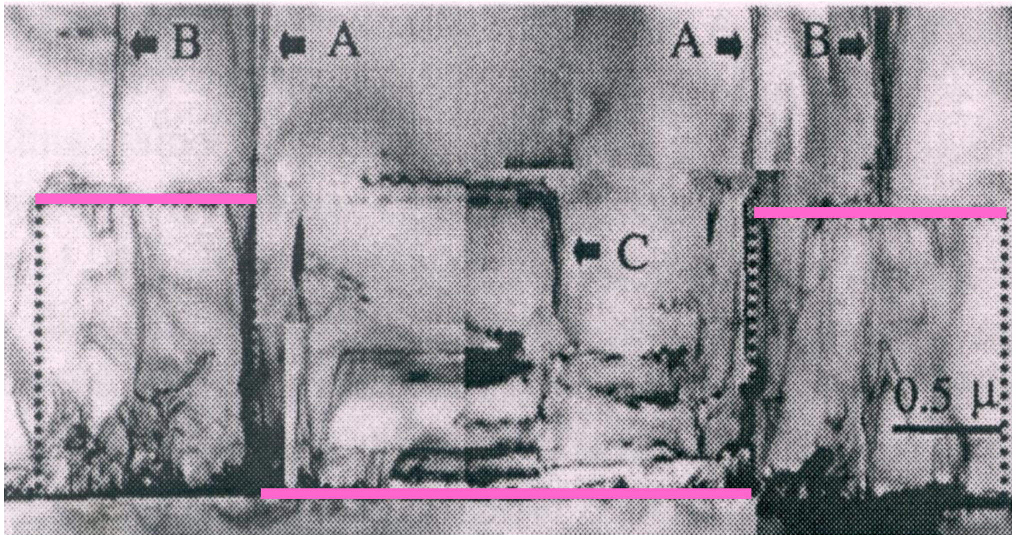
Pendeo-epitaxy

Chen et al. APL 1999





TEM

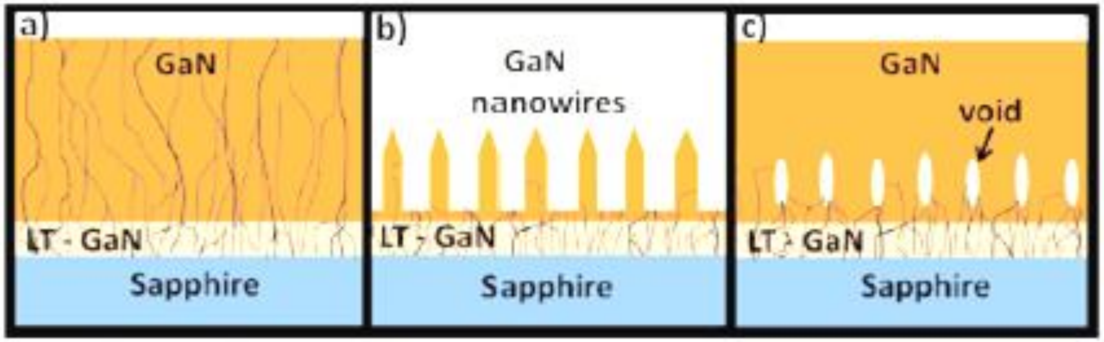


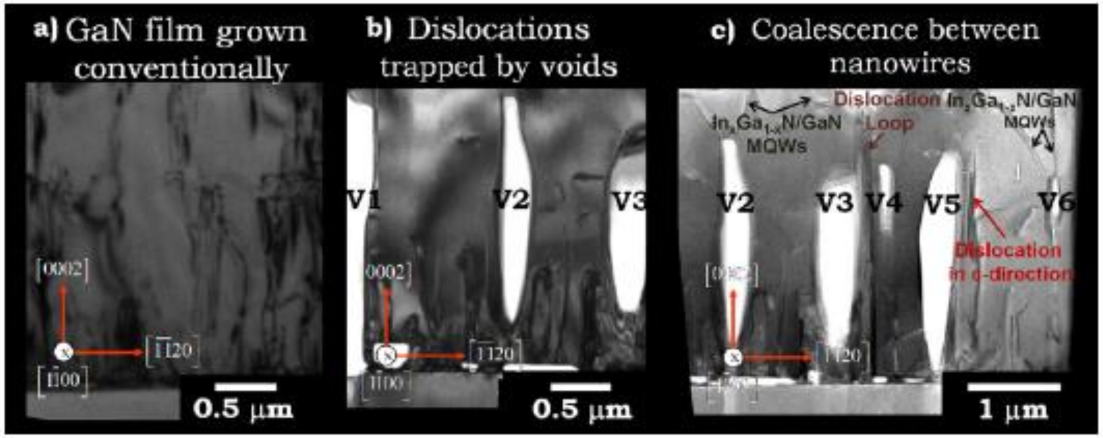
Advantage: maskless versions of PE possible for GaN on SiC or SiC-coated Si

Strittmatter et al. APL 2001; Davis et al. JCG 2001

EVA – Embedded Void Approach

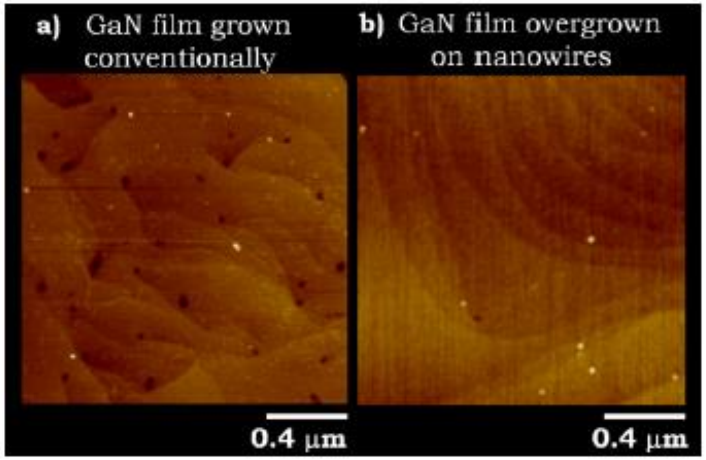
Frajtag et al. APL 2011 ***98*** *023115*





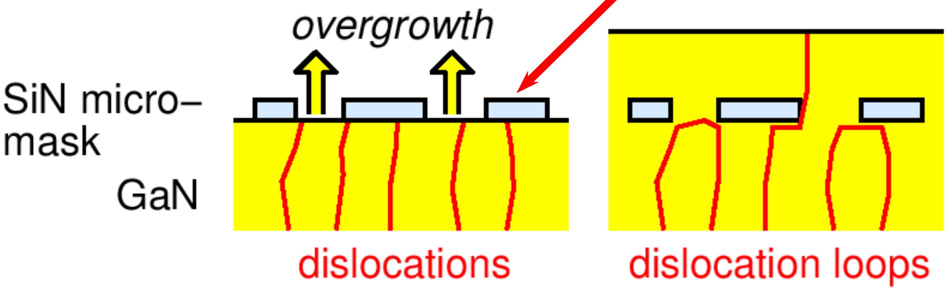
TEM

2.1×10^{9} cm^{-2} 3.9×10^{7} cm^{-2}



AFM

“random” mask (SiN coverage below 1 ML)



overgrowth

SiN micro–mask

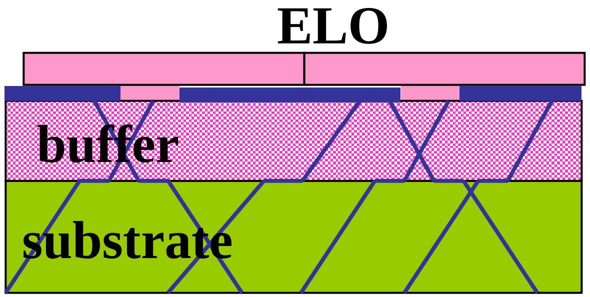
GaN

dislocations

dislocation loops

S. Tanaka *et al.*, Jpn. J. Appl. Phys. **39**, L831 (2000)

ELO summary



a tool for fabrication of low-dislocation density epilayers on heavily dislocated substrates

take from the seed info on crystal lattice; do not take defects!!!

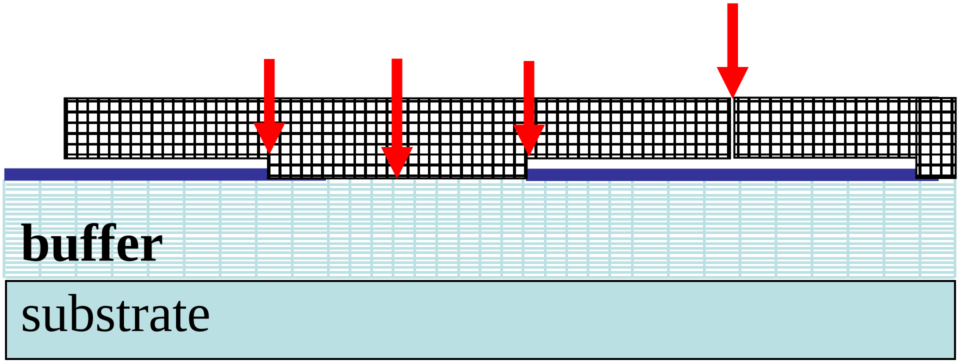
ELO – all lattice mismatch-induced problems solved?

Achievements:

1. significant reduction of dislocation density in lattice-mismatched heterostructures
2. easier elastic relaxation of thermal strain

Problems:

1. interaction of ELO layers with the mask; bending
2. generation of defects at the front of coalescence



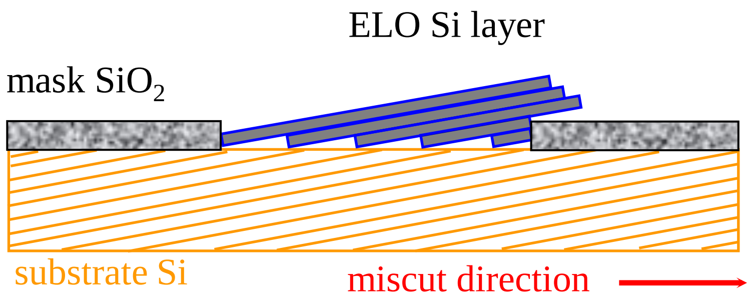
Mechanism of ELO growth on dislocated substrates

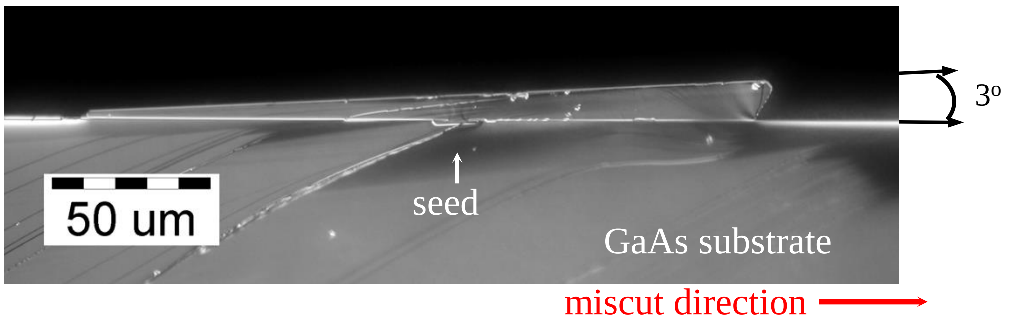
comparison

ELO on dislocation-free substrate
Si/Si

ELO on dislocated substrate
GaAs/GaAs

Zytkiewicz et al. Cryst. Res. Technol. 2005





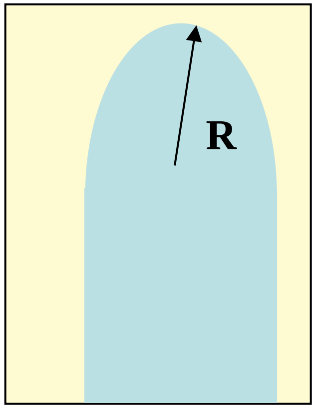
growth in the miscut direction only
(for low supersaturation)

growth in all directions

on dislocated substrate ELO growth possible w/o substrate miscut
(miscut used sometimes though; e.g GaAs/Si)

Gibbs-Thomson effect ⇒ S. Krukowski's lecture

Gibbs – Thomson effect a – phase equilibrium on curved surface depends on radius of phase boundary

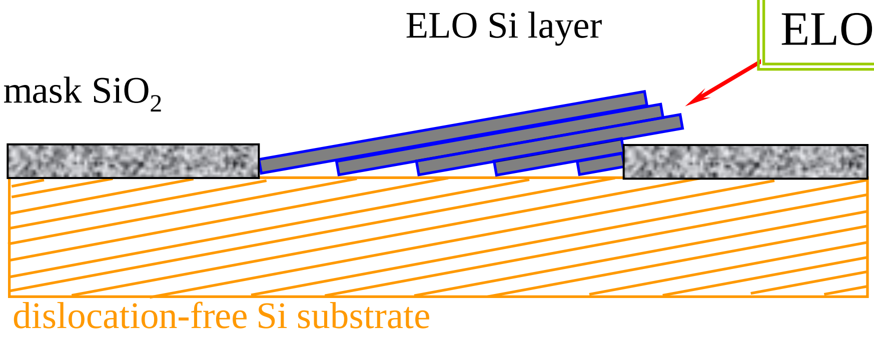


Γ - capillarity constant (~ 10^{-7} cm = 1 nm)

$$p(R) = p(\infty) \cdot \left(1 + \frac{\Gamma}{R}\right)$$

$$C(R) = C(\infty) \cdot \left(1 + \frac{\Gamma}{R}\right)$$

equilibrium pressure (solute concentration) on curved surface is larger than on the planar one



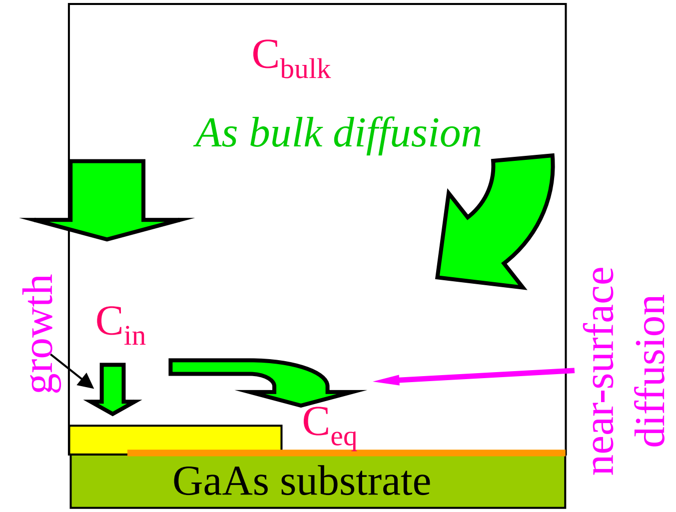
large curvature (small R) at the beginning of LPE ELO growth

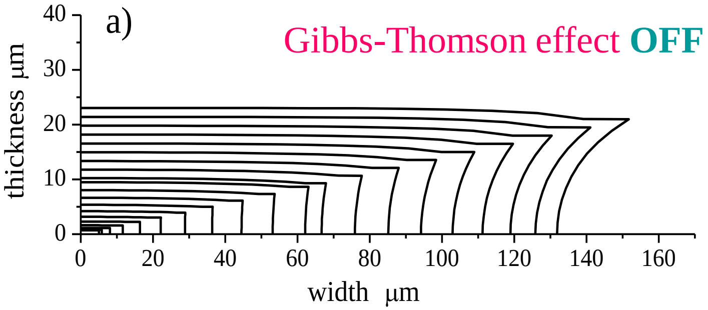
Silier et al. J. Cryst. Growth 1996

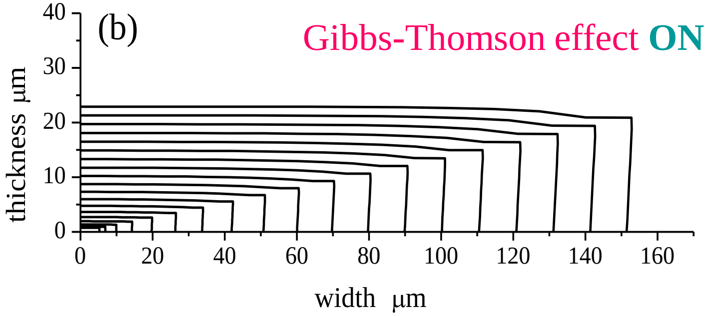
initial liquid supercooling ~1.8°C needed to allow the ELO layer to get out of the channel over the mask

Gibbs-Thomson effect ⇒ S. Krukowski's lecture

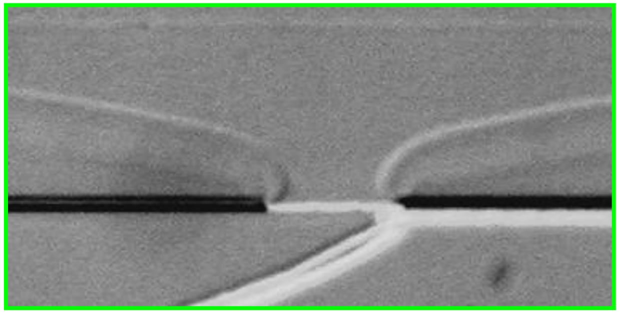
simulations: ELO of GaAs byLPE

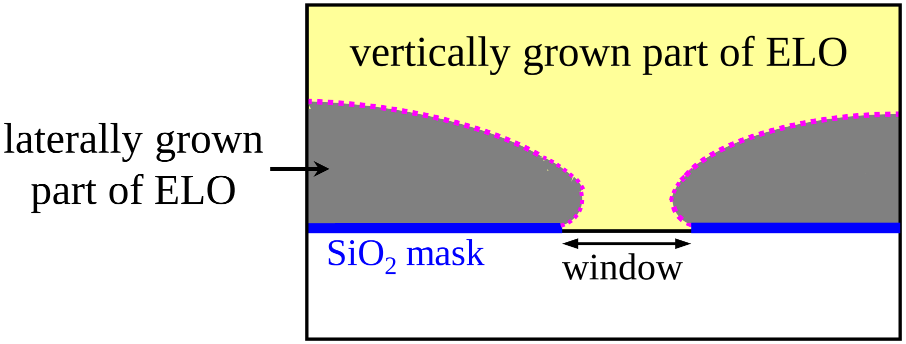






Gibbs-Thomson effect:
ELO of GaAs by LPE

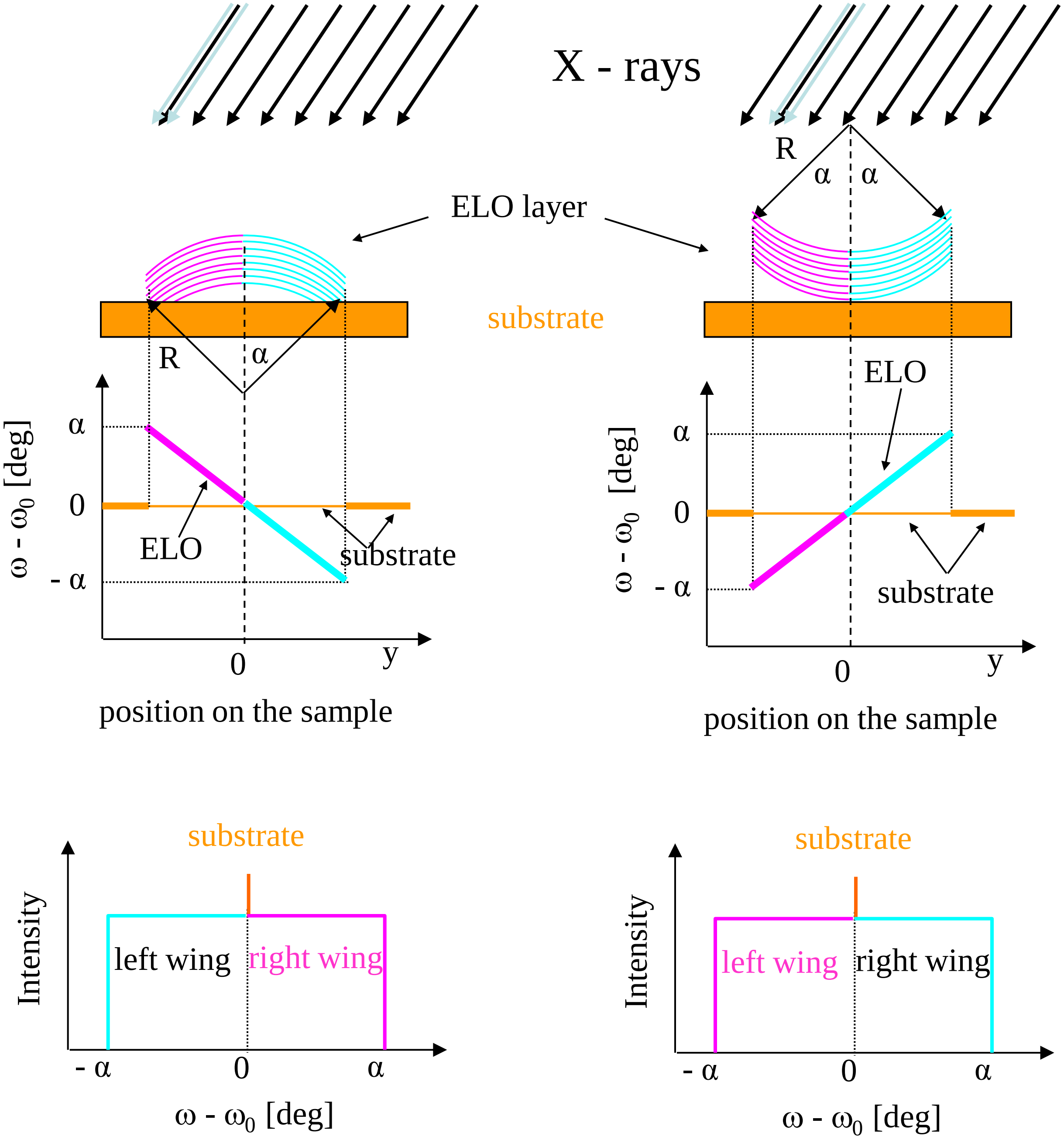




substrate dislocations make ELO growth possible without initial supersaturation of the solution

Lokalna XRD - przykład

⊗ sample rotation axis in the ω sc



SRXRD mapping:

tilt angle α(y) can be measured

- tilt direction easy to determine
- curvature radius R(y) can be measured locally
- shape of lattice planes can be analyzed α(y) ~ h’(y)
- width of ELO can be measured

Standard Rocking Curve:

- tilt angle α can be measured
- tilt direction cannot be determined